

**DESIGN, FABRICATION AND
TESTING OF MONOLITHIC LOW-
POWER PASSIVE SIGMA-DELTA
ANALOG-TO DIGITAL-
CONVERTERS**

by
Angsuman Roy

A BRIEF ROADMAP

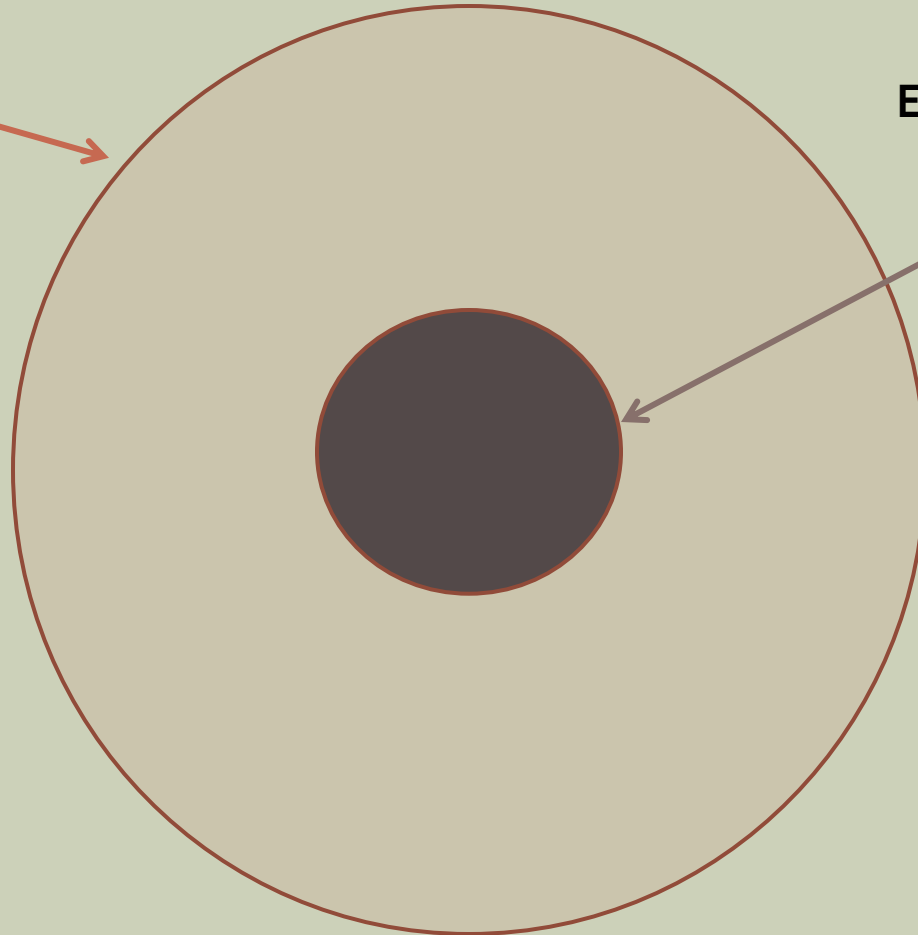
- Context
- Basic Sigma-Delta ADC Concepts
- Review of Passive Sigma-Delta Topologies
- Proposed Topology
- Continuous-Time IC Implementation
- Switched-Capacitor IC Implementation
- KD1S IC Implementation

FITTING IN

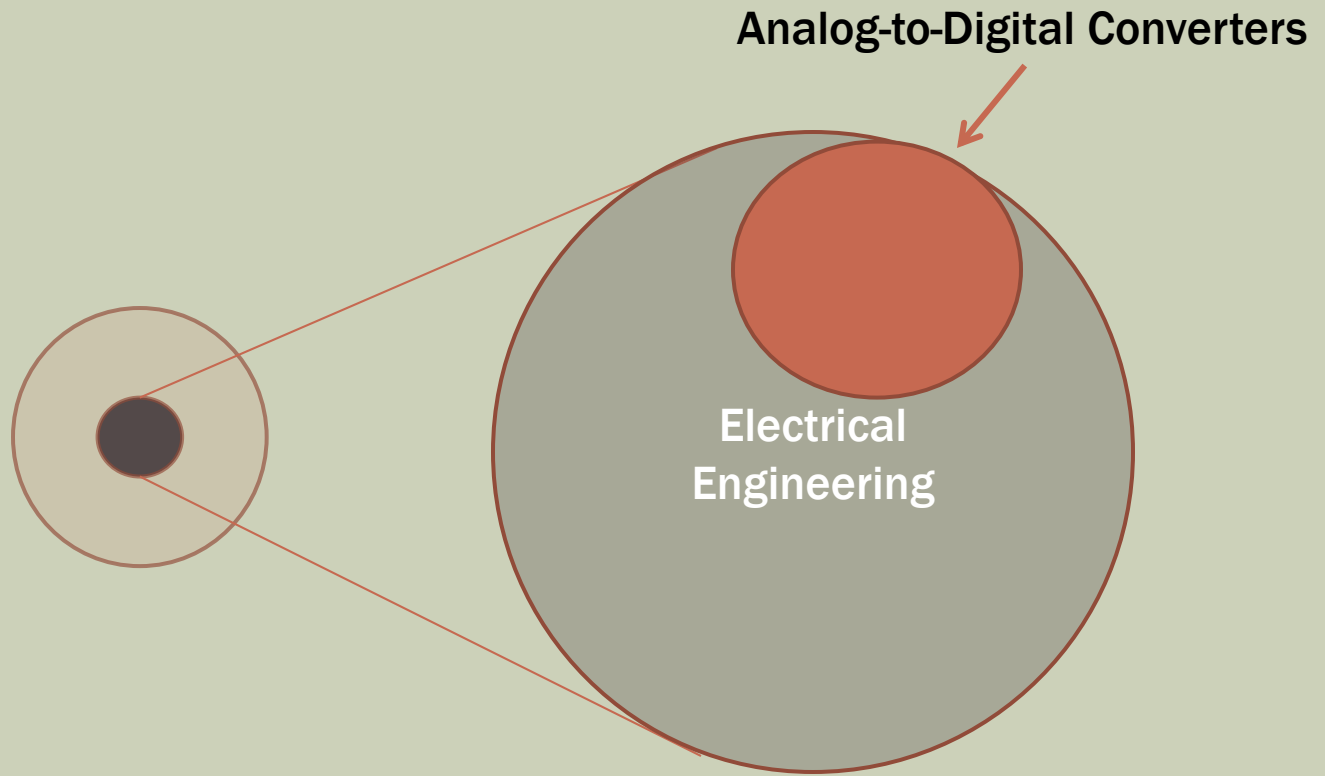
All Knowledge



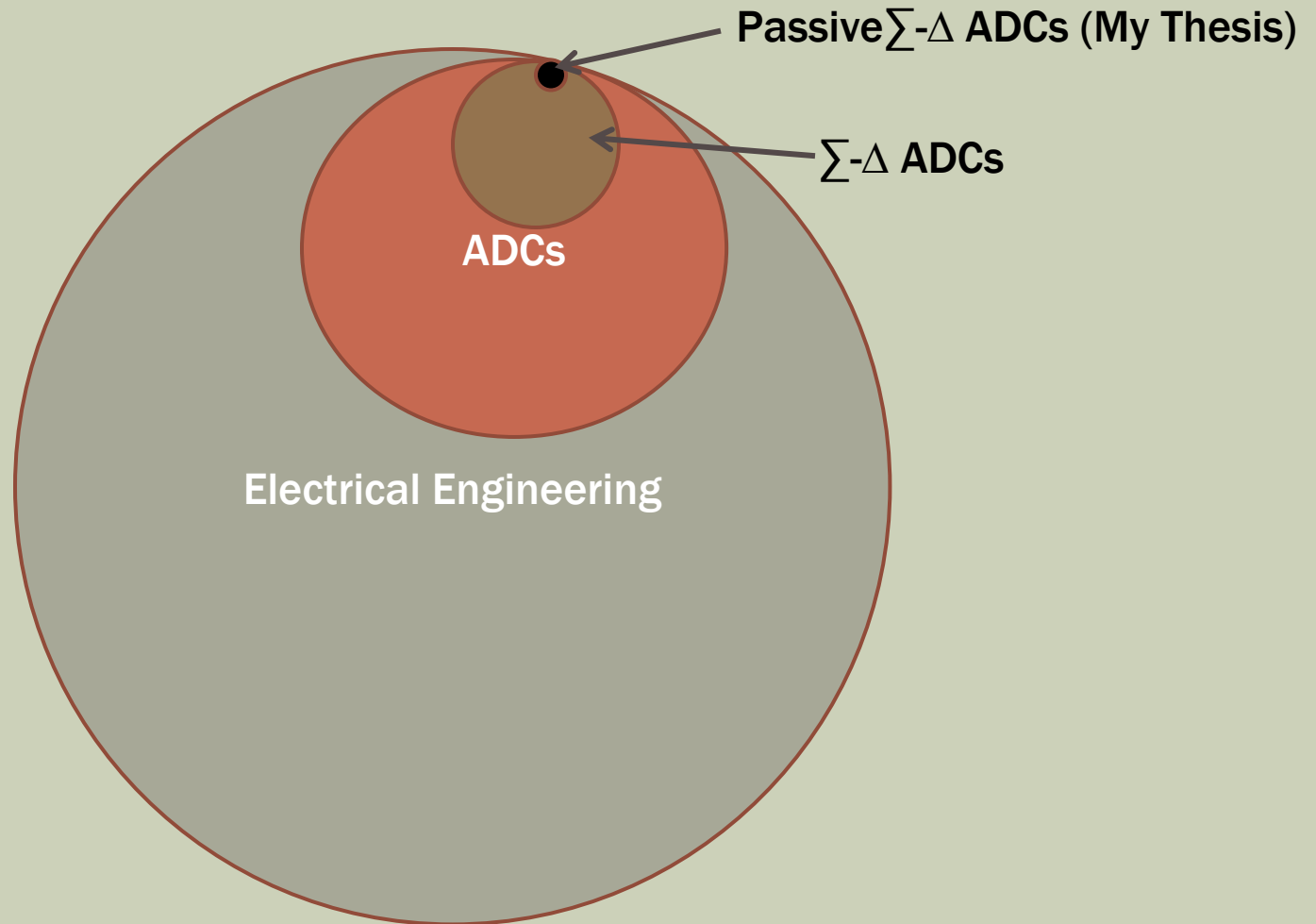
Electrical Engineering



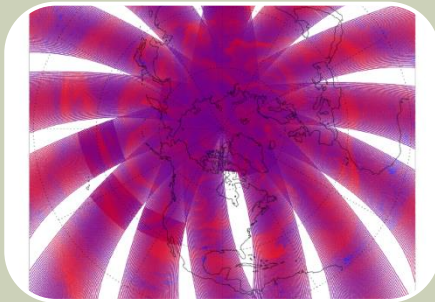
FITTING IN



FITTING IN



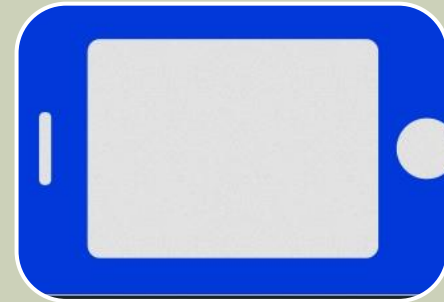
MARKET NEED FOR LOW POWER Σ - Δ ADC



Remote Sensing



Internet of Things



Mobile Devices

All these future devices and trends require low cost, low power ADCs.
High resolution and precision are not prioritized.
Passive Σ - Δ ADCs can meet this need.

ANALOG-TO-DIGITAL CONVERTERS

Nyquist Rate ADCs



Flash
SAR
Pipeline

- Sampling rate is at least twice the input bandwidth.
- Resolution is limited to nominal value.

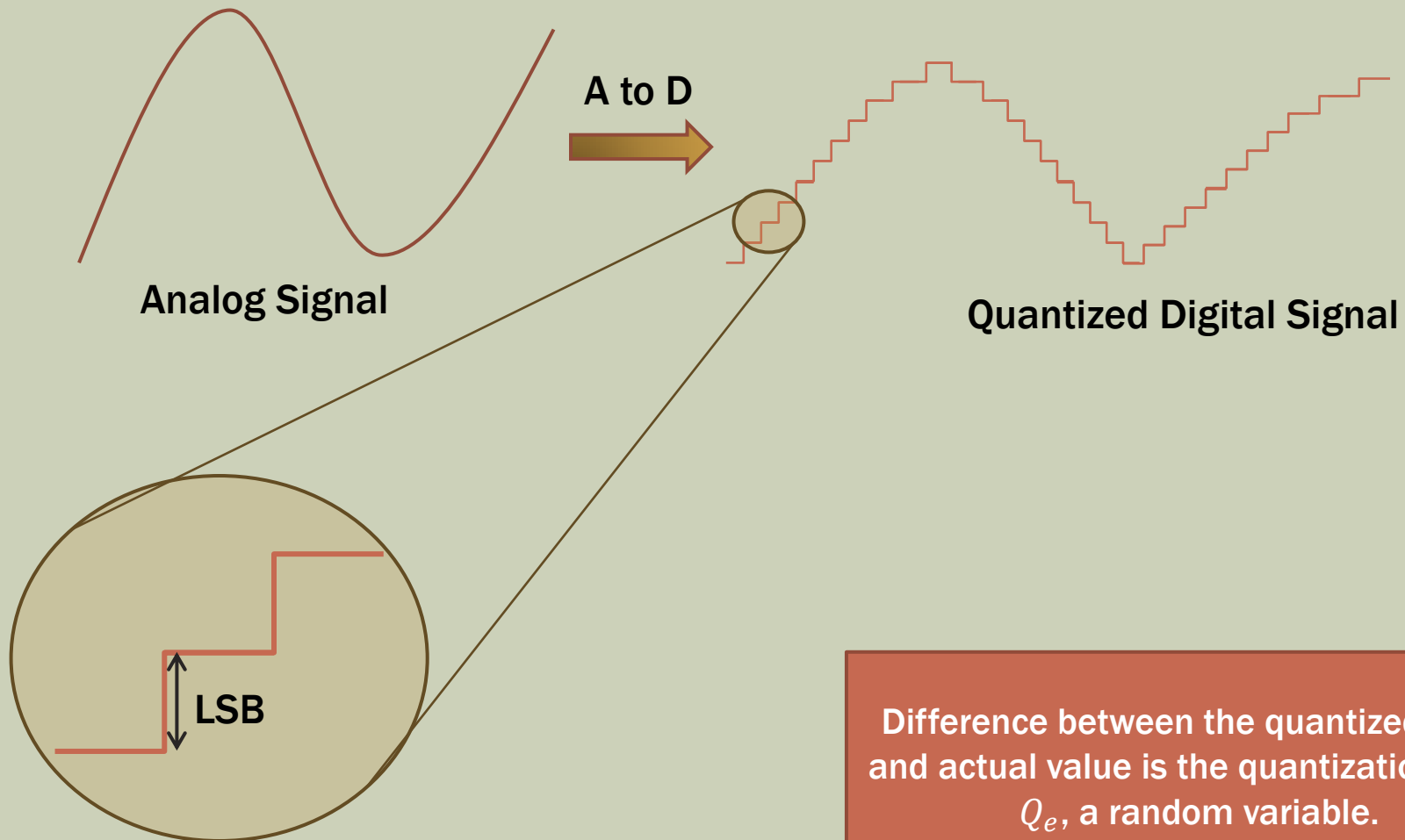
Oversampling ADCs



Sigma-Delta

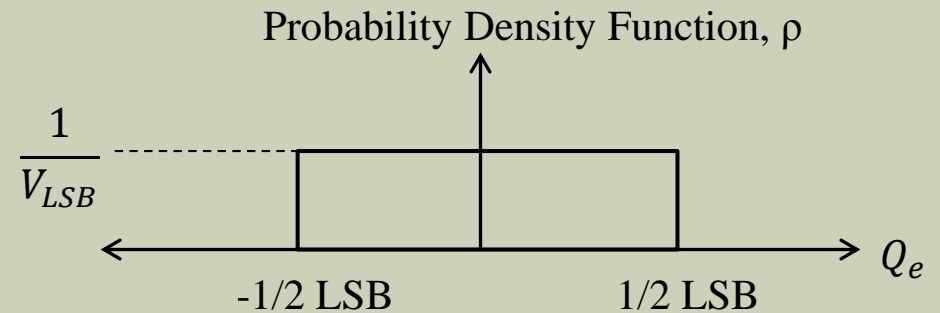
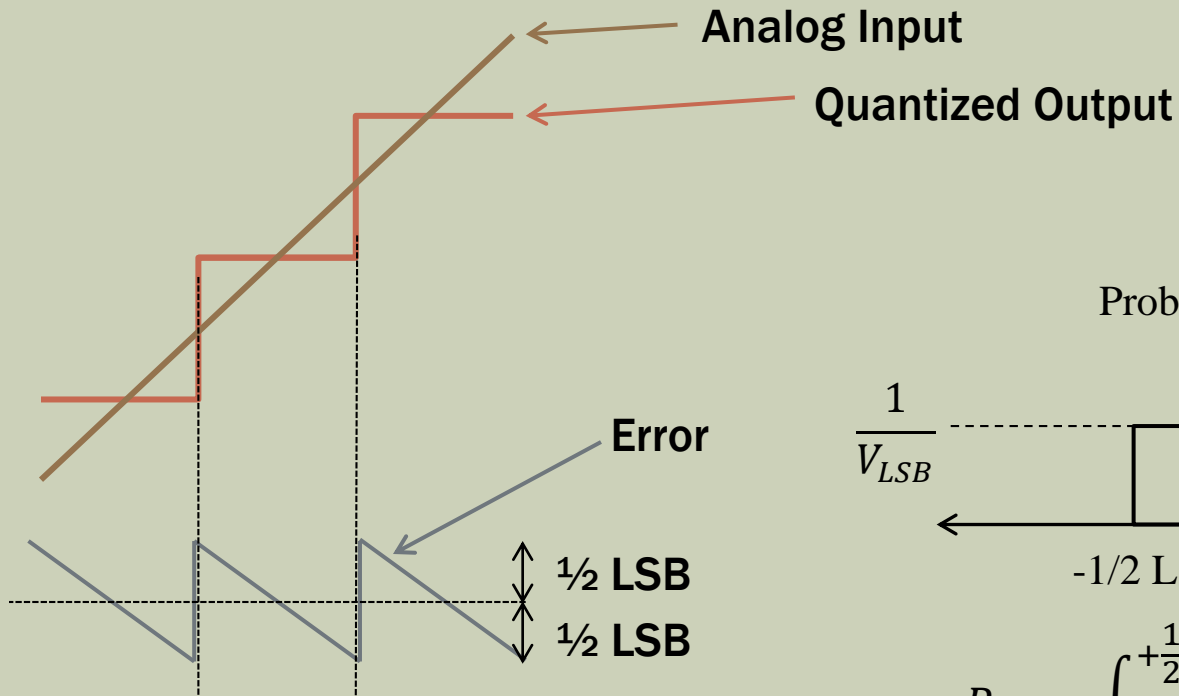
- Sampling rate is much higher than input bandwidth.
- Resolution is higher than the nominal value.

QUANTIZATION ERROR



Difference between the quantized value and actual value is the quantization error, Q_e , a random variable.

QUANTIZATION ERROR

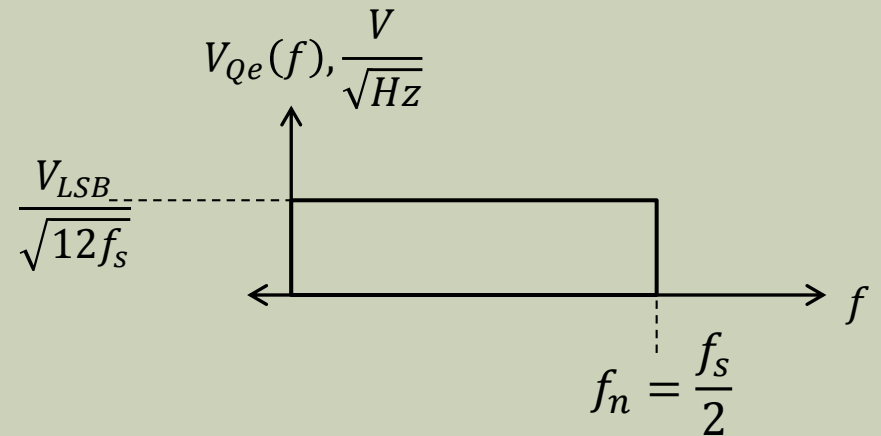
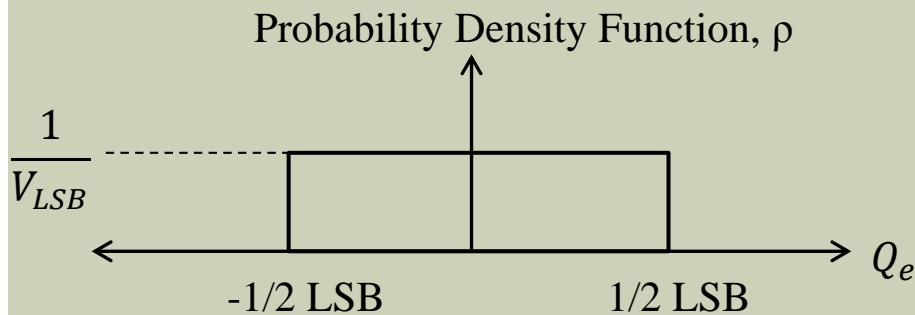


$$P_{Q_e} = \int_{-\frac{1}{2} LSB}^{+\frac{1}{2} LSB} \rho * (Q_e) * dQ_e = \frac{V_{LSB}^2}{12}$$

$$V_{Q_e, RMS} = \frac{V_{LSB}}{\sqrt{12}}$$

PDF AND PSD OF QUANTIZATION ERROR

$$P_{Q_e} = \int_{-\frac{1}{2}LSB}^{+\frac{1}{2}LSB} \rho * (Q_e) * dQ_e = \frac{V_{LSB}^2}{12} = 2 * \int_0^{\frac{f_s}{2}} V_{Q_e}^2(f) * df$$



Key

P_{Q_e} : Quantization Noise Power

Q_e : Quantization Error

V_{LSB} : Least-Significant-Bit Voltage

$V_{Q_e}(f)$: Quantization Noise Voltage

$V_{Q_e}^2(f)$: Quantization Noise Power Spectral Density

f_n : Nyquist Frequency

f_s : Sampling Frequency

OVERSAMPLING

Oversampling is running a data converter at a sampling rate beyond the Nyquist criterion in order to increase its resolution.

Nyquist Criterion

$$f_{\text{sampling}} = 2f_{\text{MAX}}$$

Oversampling Ratio

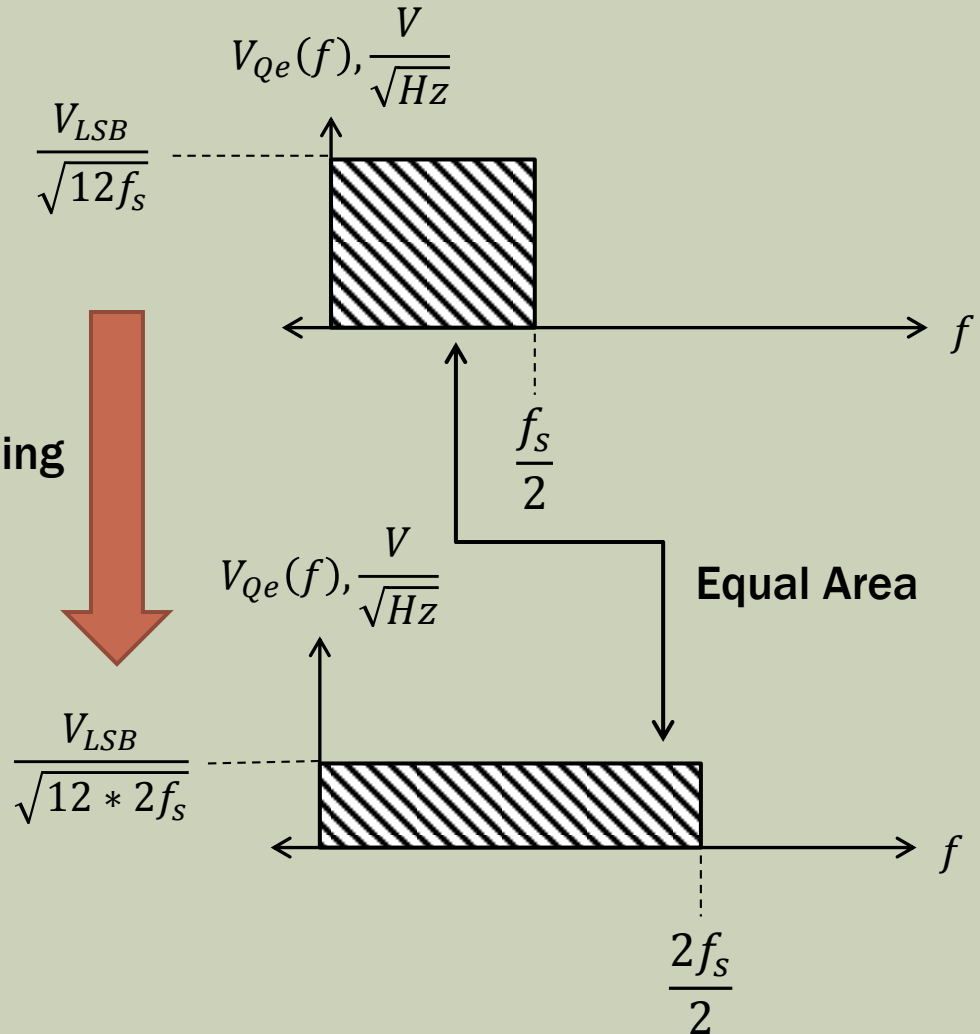
$$OSR = 2^{2n}$$

QUANTIZATION NOISE

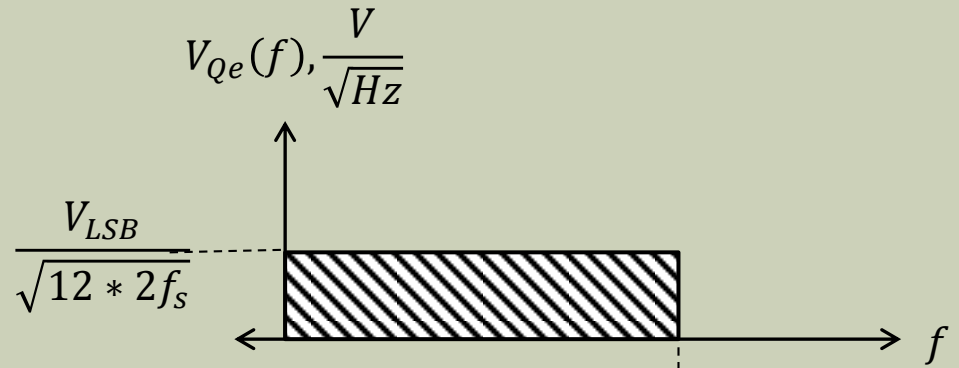
RMS quantization noise
is the same regardless
of sampling frequency.

But the distribution as a
function of frequency is
different.

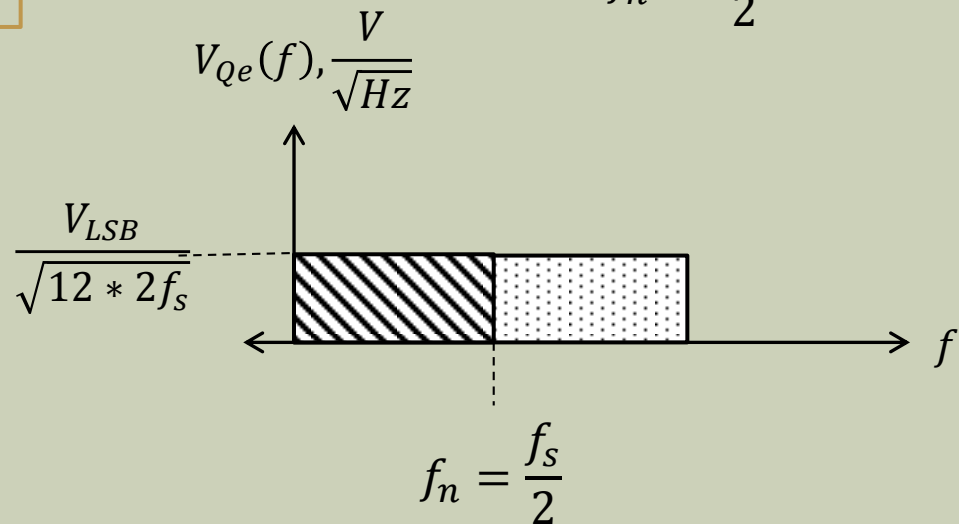
2X Sampling



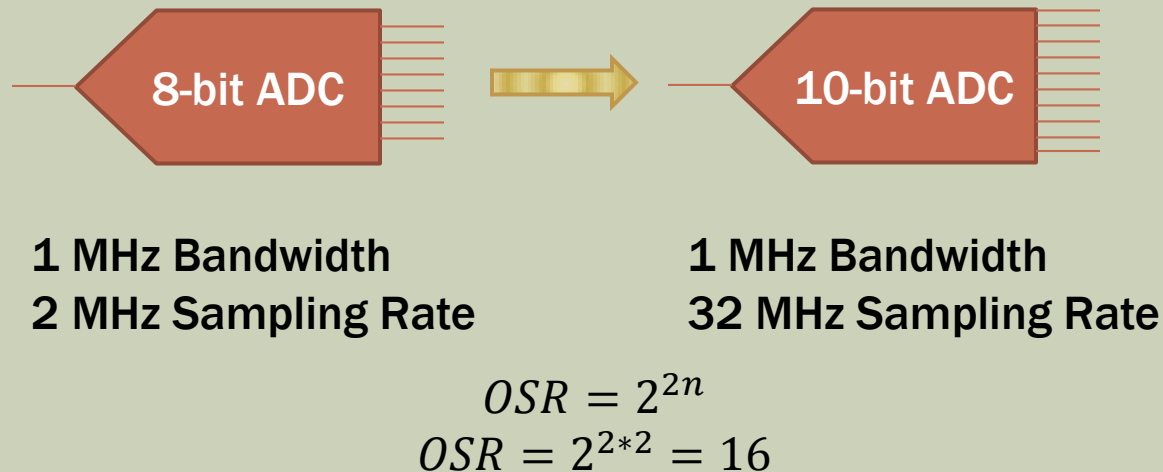
BANDLIMITING



Bandlimiting reduces quantization noise by restricting bandwidth.



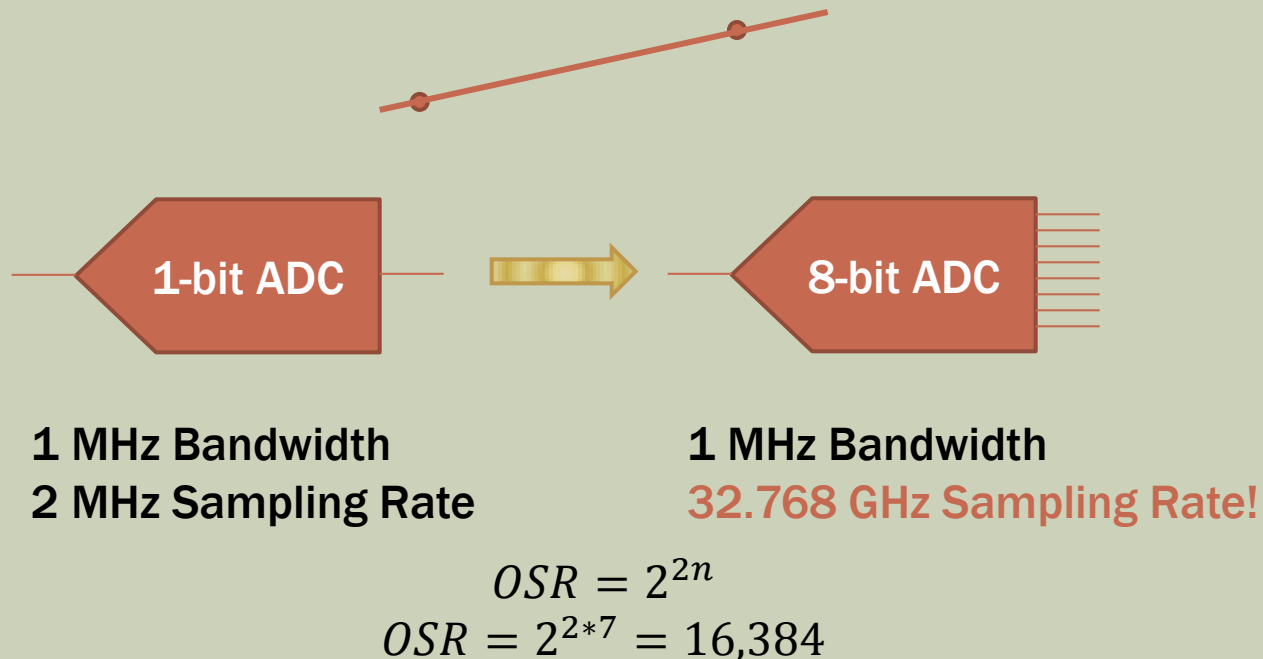
OVERSAMPLING EXAMPLE



Caveat Inherent linearity of data converter must be equal to desired resolution.

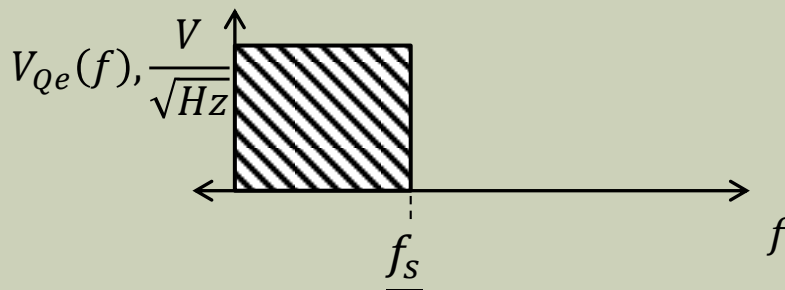
1-BIT ADC

Solution A 1-bit ADC is inherently linear because two points define a perfectly straight line.

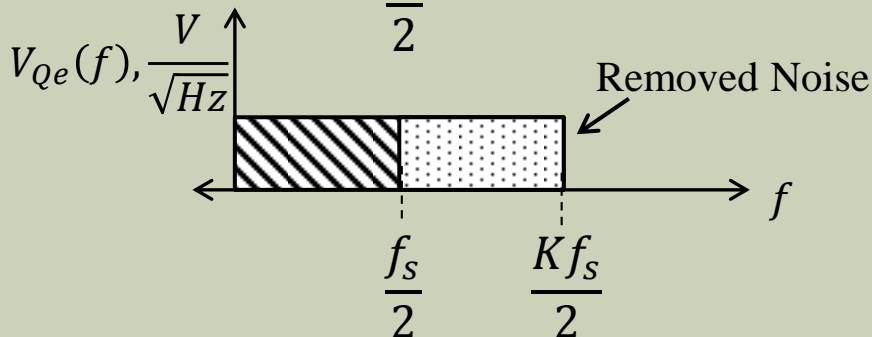


NOISE SHAPING

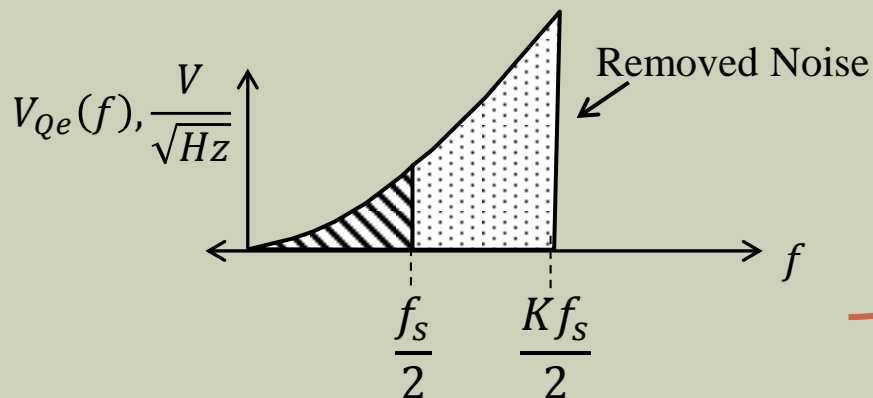
Nyquist Rate



Simple
Oversampling



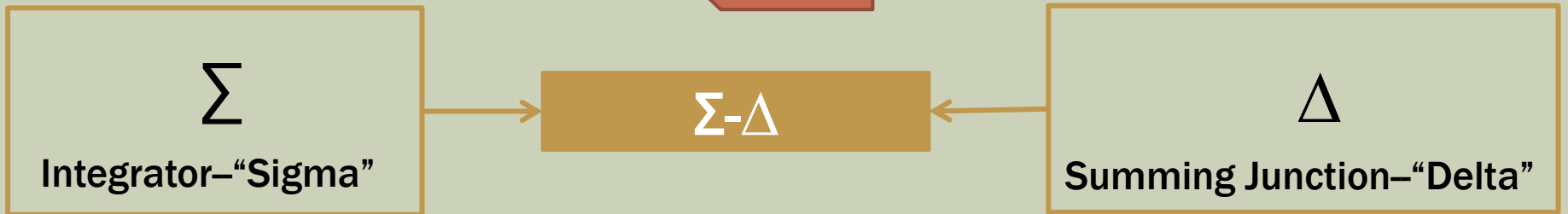
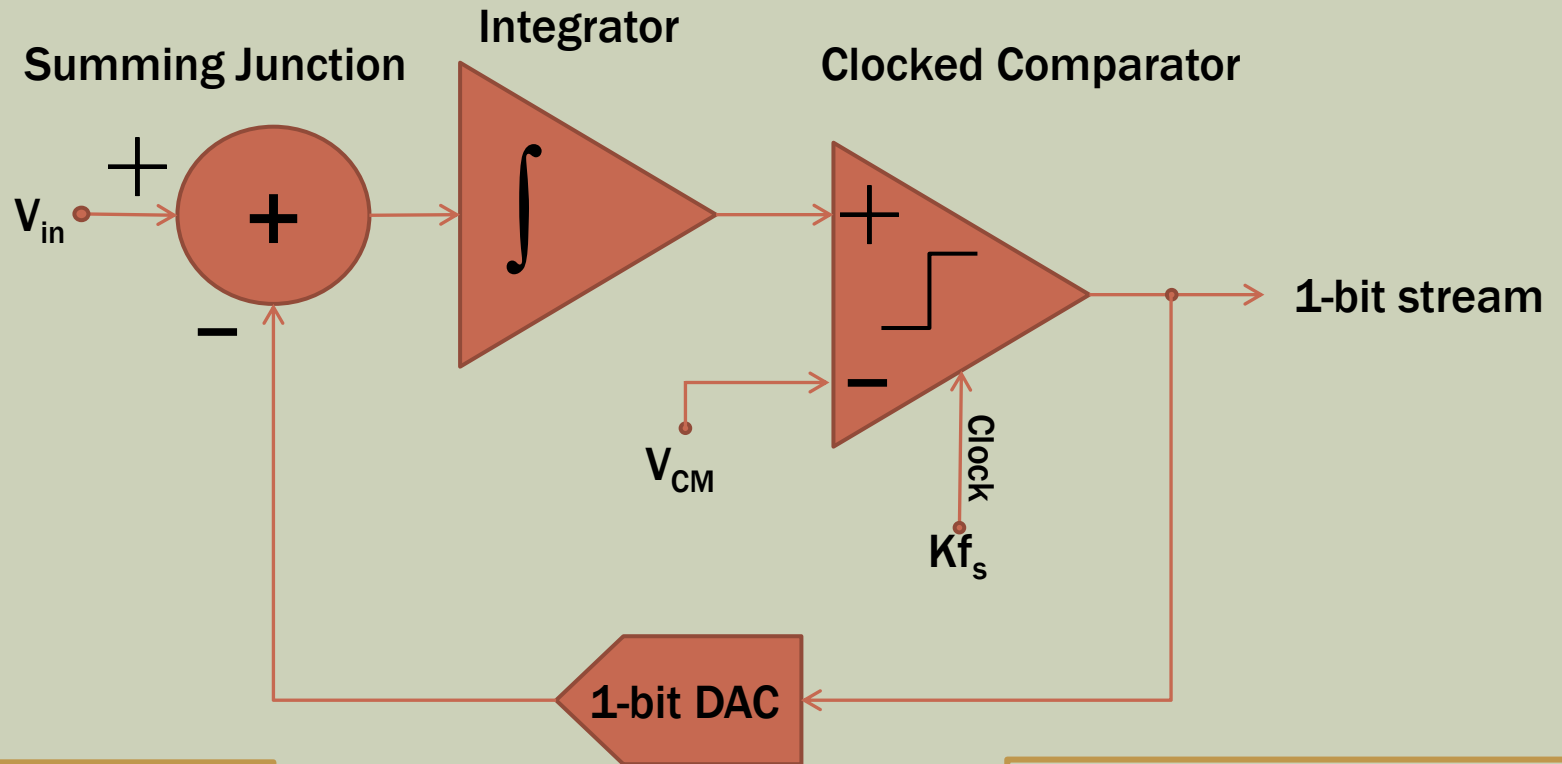
Oversampling
with Noise
Shaping



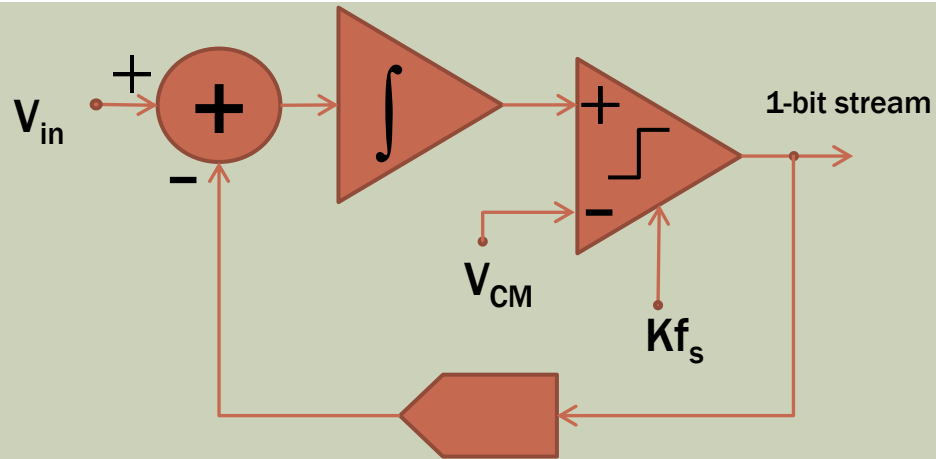
RMS quantization
noise, $V_{Qe,RMS}$
remains $\frac{V_{LSB}}{\sqrt{12}}$

in all examples but
bandlimiting reduces
noise in the signal
bandwidth.

BASIC 1ST ORDER Σ - Δ MODULATOR

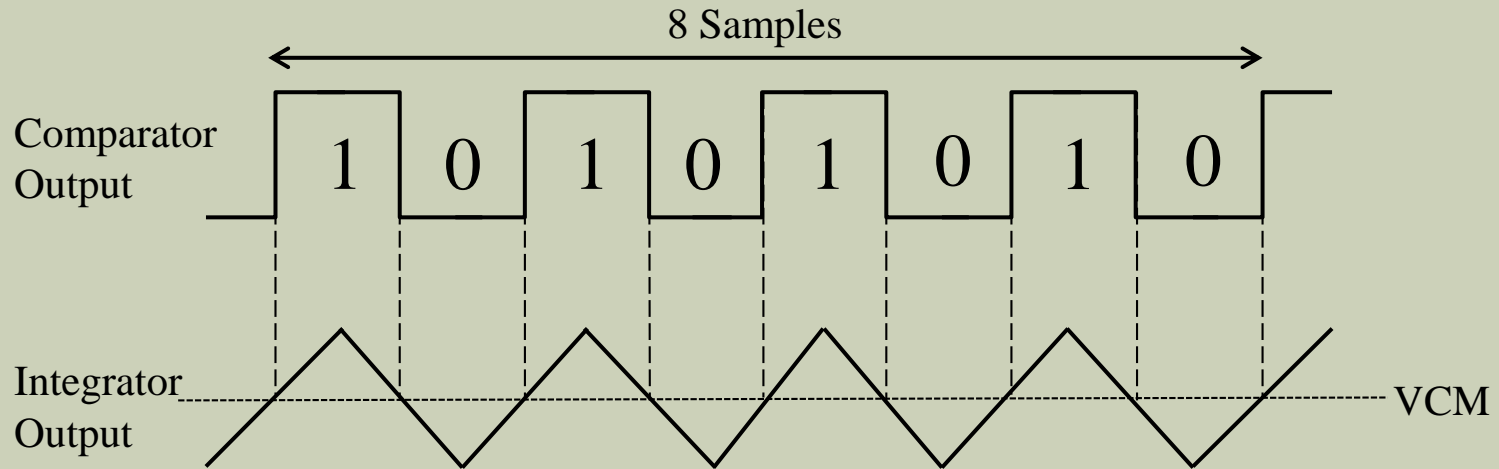


Σ - Δ MODULATOR WITH DC INPUT

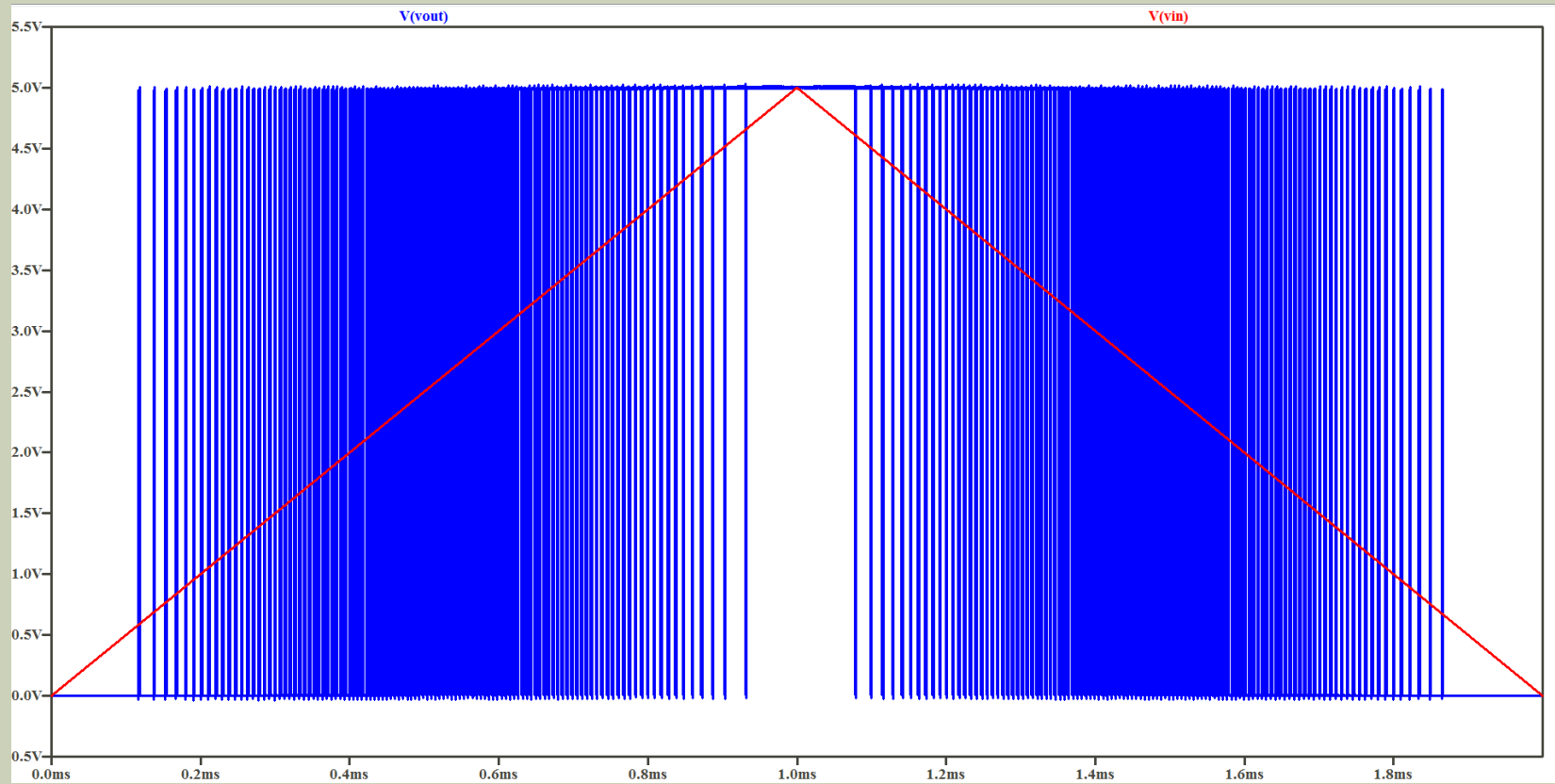


$Input = V_{CM} = \frac{1}{2} * Full\ Scale\ Voltage$

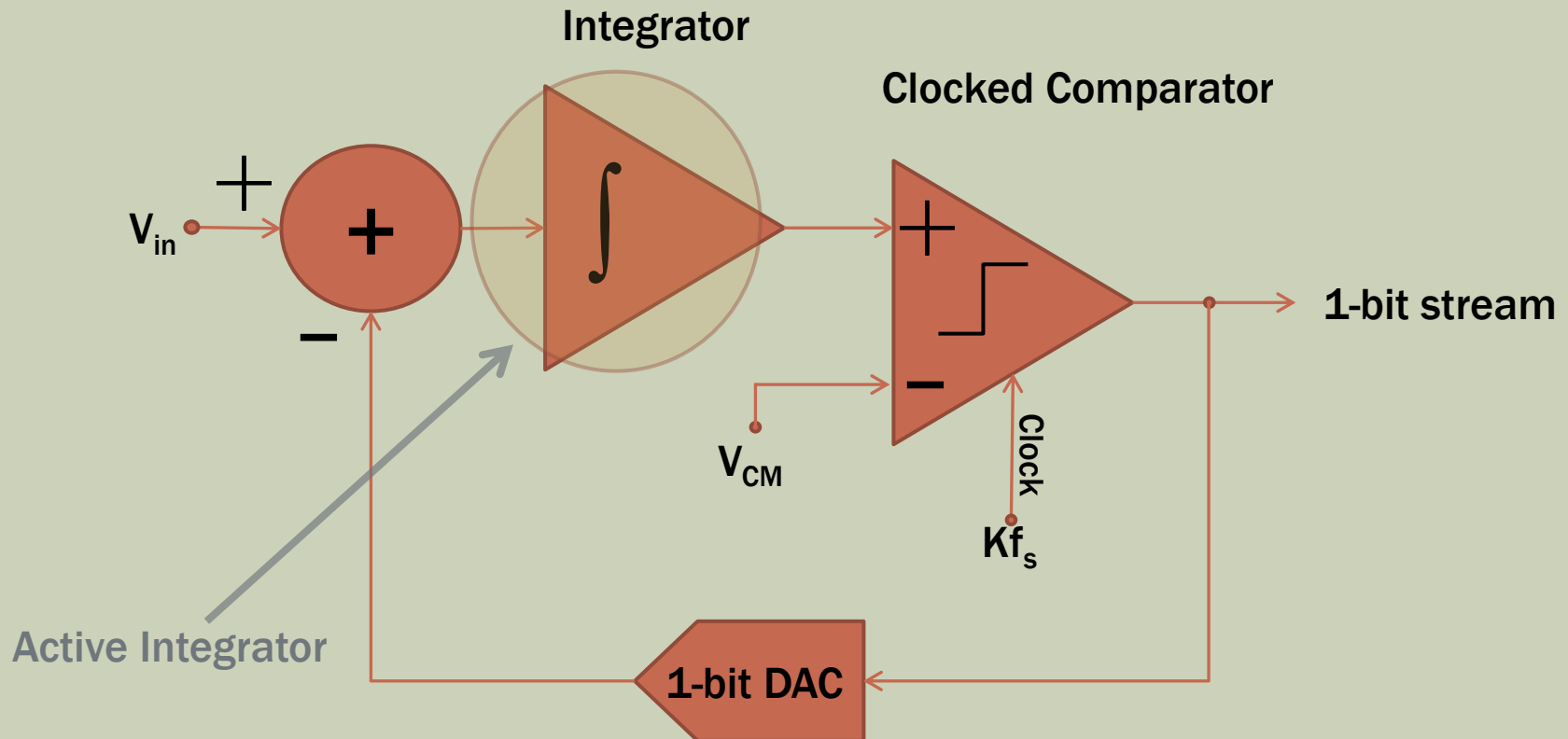
$Average\ Output = \frac{1 + 1 + 1 + 1}{8} = \frac{1}{2}$



1-BIT OUTPUT



BASIC 1ST ORDER Σ - Δ MODULATOR



Generally, Σ - Δ modulators use an active integrator to keep the **voltage swing** on the integrator's input to a **minimum** (ideally zero).

WHY PASSIVE?

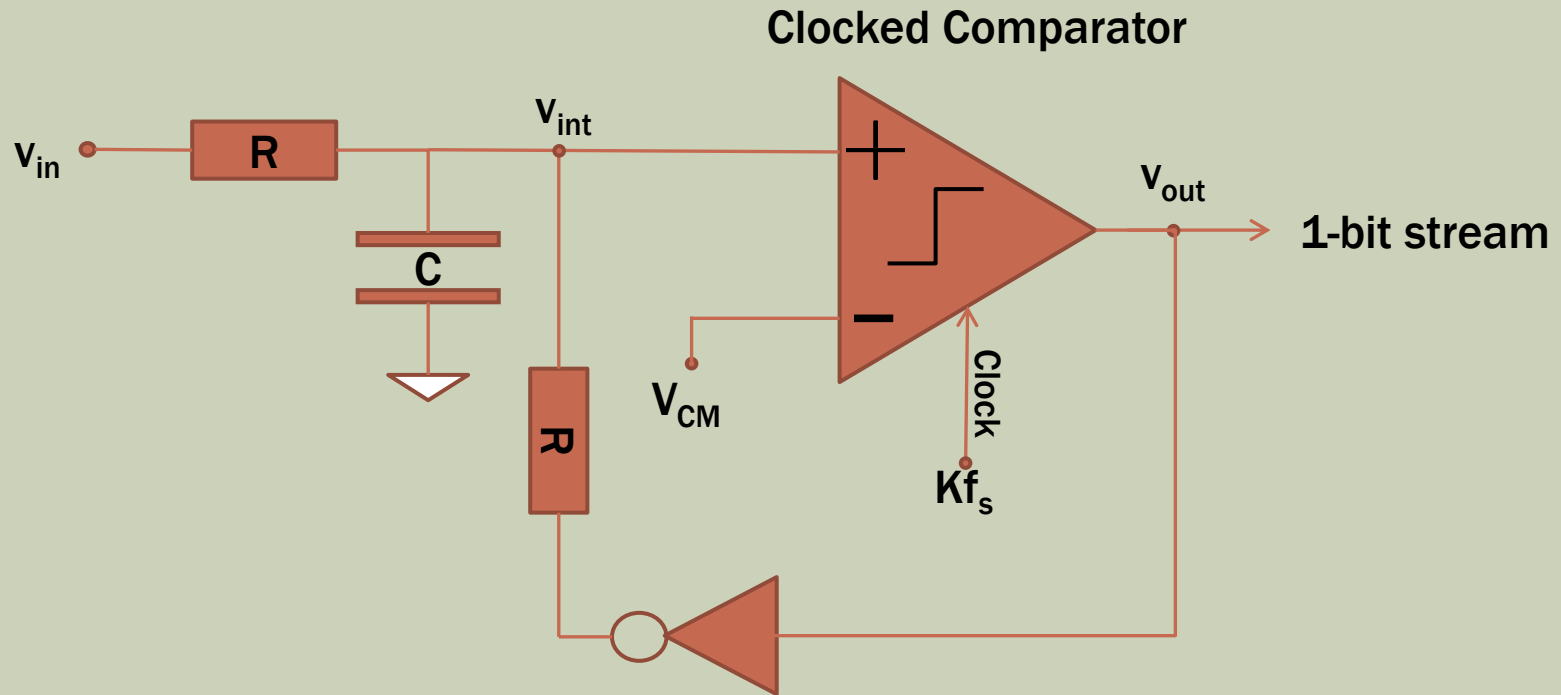
Lower Power

- Active integrators constantly draw current for biasing.
- Passive modulators only draw current while switching.

Higher Speed

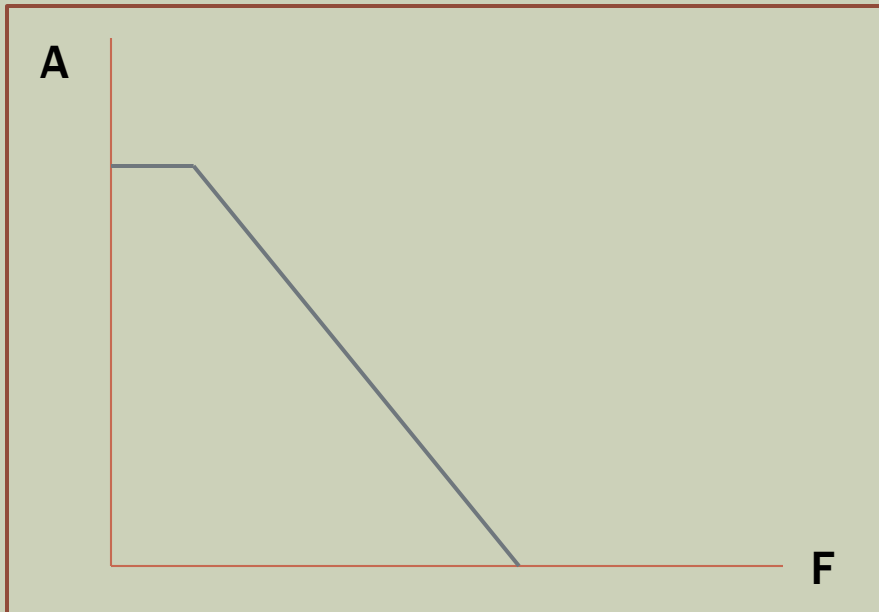
- Passive modulators are not limited by op-amp GBW performance.

1ST ORDER PASSIVE Σ - Δ MODULATOR



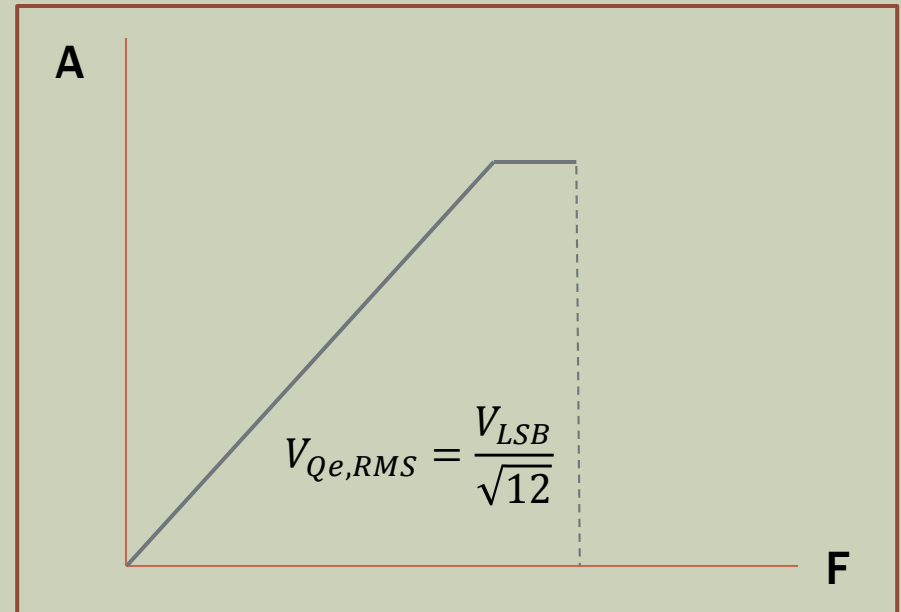
$$v_{out} = \underbrace{\frac{1}{1 + sRC}}_{\text{STF}} \cdot v_{in} + \underbrace{\frac{sRC}{1 + sRC}}_{\text{NTF}} \cdot V_{qe} + \underbrace{\frac{-2}{1 + sRC}}_{\text{DT (distortion term)}} \cdot v_{int}$$

TRANSFER FUNCTIONS



Signal Transfer Function Plot

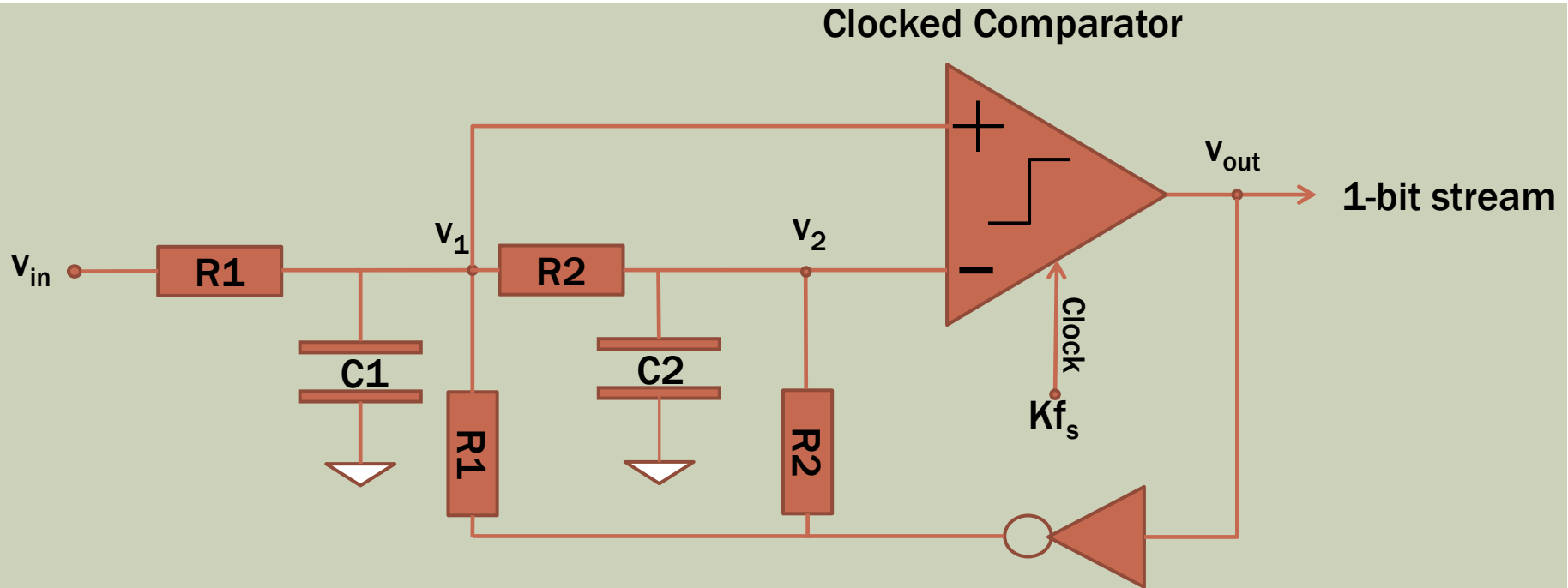
$$\frac{1}{1 + sRC}$$



Noise Transfer Function Plot

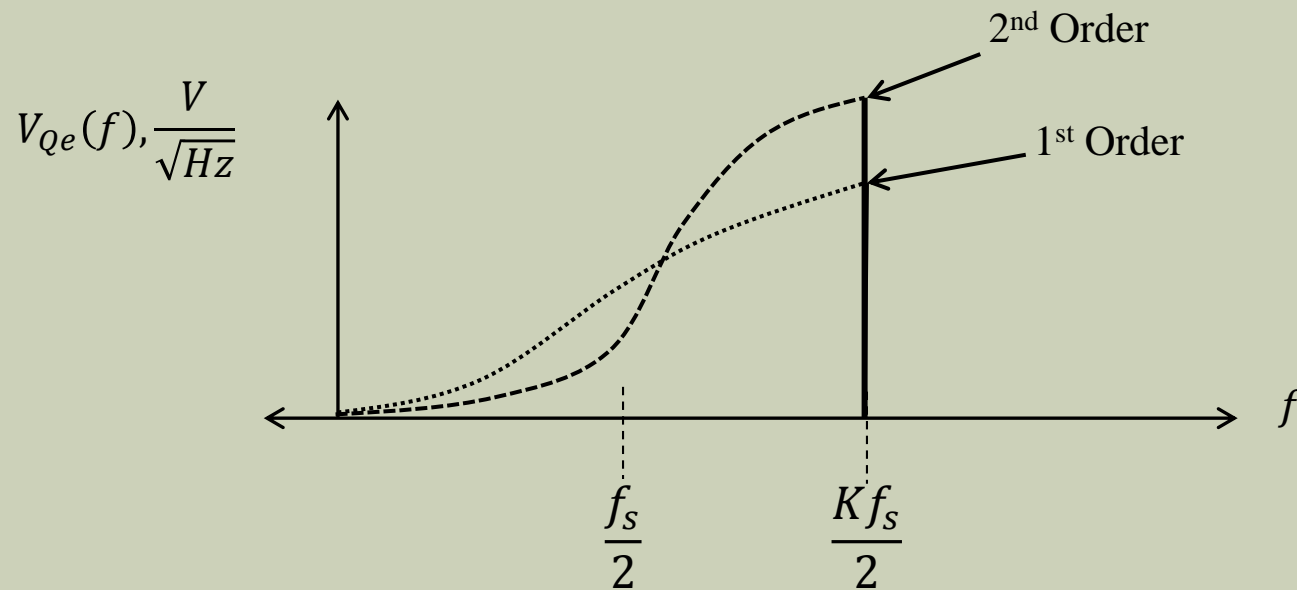
$$\frac{sRC}{1 + sRC}$$

CONVENTIONAL 2ND ORDER PASSIVE Σ - Δ MODULATOR



$$v_{out}^2 = \underbrace{\frac{1}{1 + (\omega RC)^2}}_{\text{STF}} \cdot v_{in}^2 + \underbrace{\frac{(\omega RC)^2}{1 + (\omega RC)^2}}_{\text{NTF}} \cdot \frac{V_{Qe}^2}{2} + \underbrace{\frac{2v_1 + v_2}{1 + (\omega RC)^2}}_{\text{DT (distortion term)}}$$

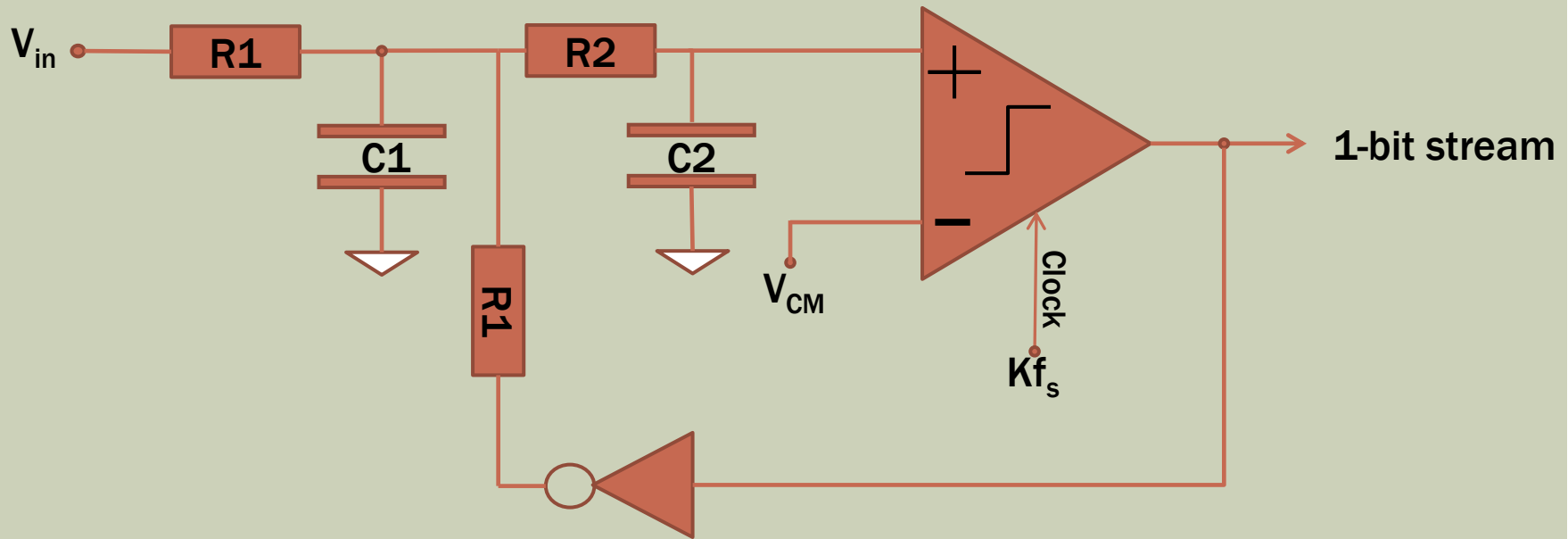
NOISE SHAPING ORDER



Increasing the order of the noise shaping reduces quantization noise within the signal bandwidth.

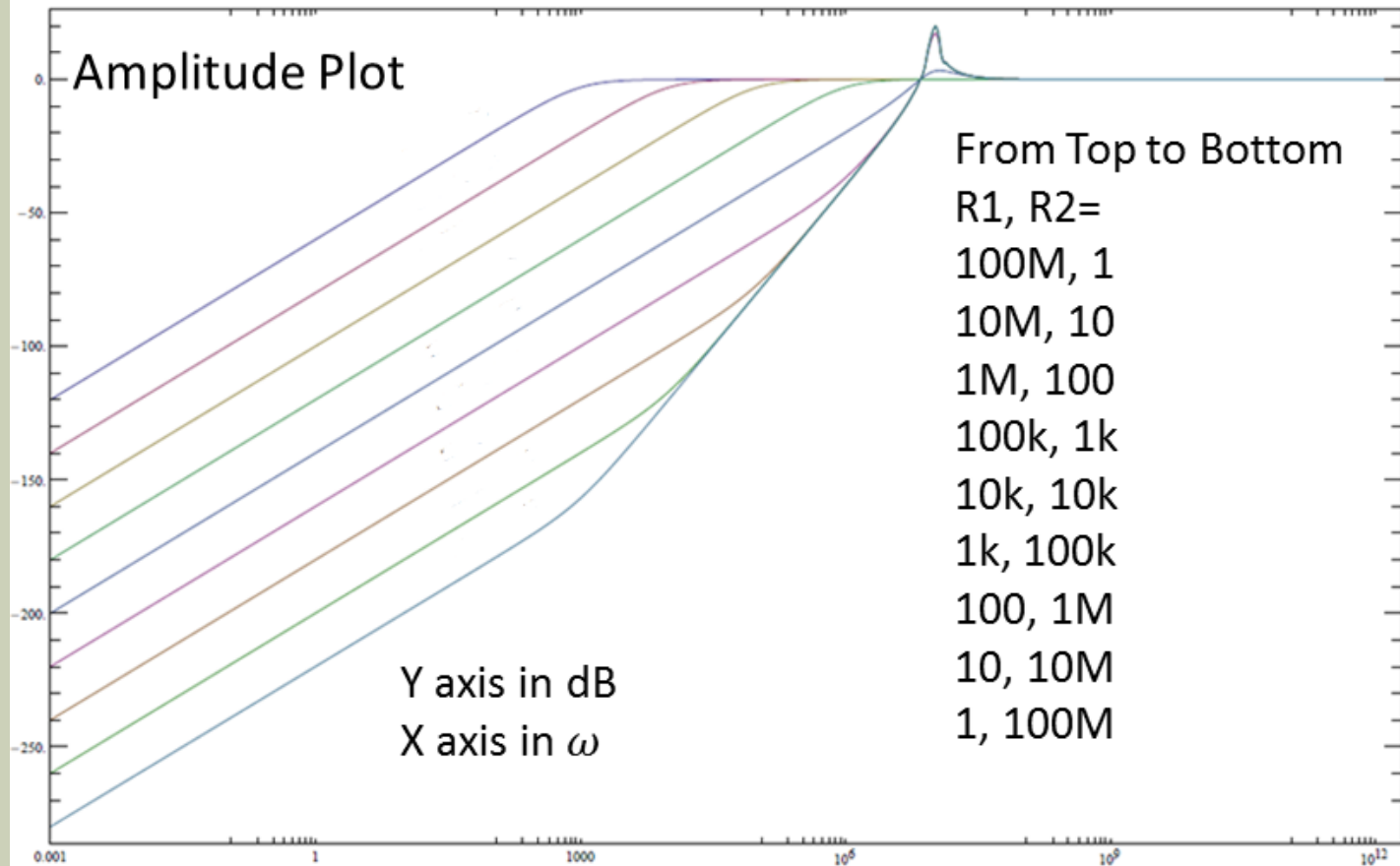
PROPOSED 2ND ORDER MODULATOR

Clocked Comparator



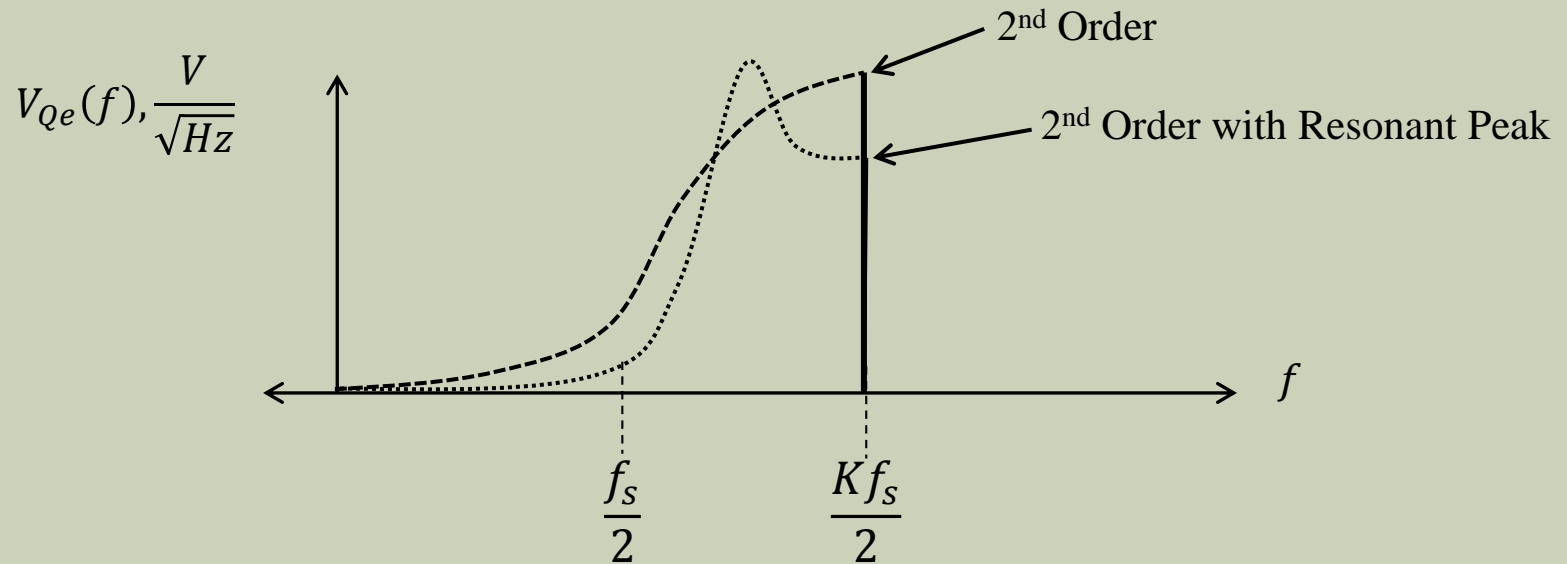
$$v_{out} = \underbrace{\frac{1 + sR_2C_2}{1 + sR_2C_2 + sR_1C_1}}_{\text{STF}} \cdot v_{in} + \underbrace{\frac{s(sR_1C_1R_2C_2 + R_1C_1)}{1 + sR_1C_1 + s^2R_1C_1R_2C_2}}_{\text{NTF}} \cdot V_{Qe} + \underbrace{\frac{1}{1 + sR_1C_1 + (1 + sR_2C_2)}}_{\text{DT (distortion term)}} \cdot v_{int}$$

MATHEMATICA PLOT OF NTF



Quantization noise is shifted to a resonant peak.

CONCEPTUAL NTF PLOT



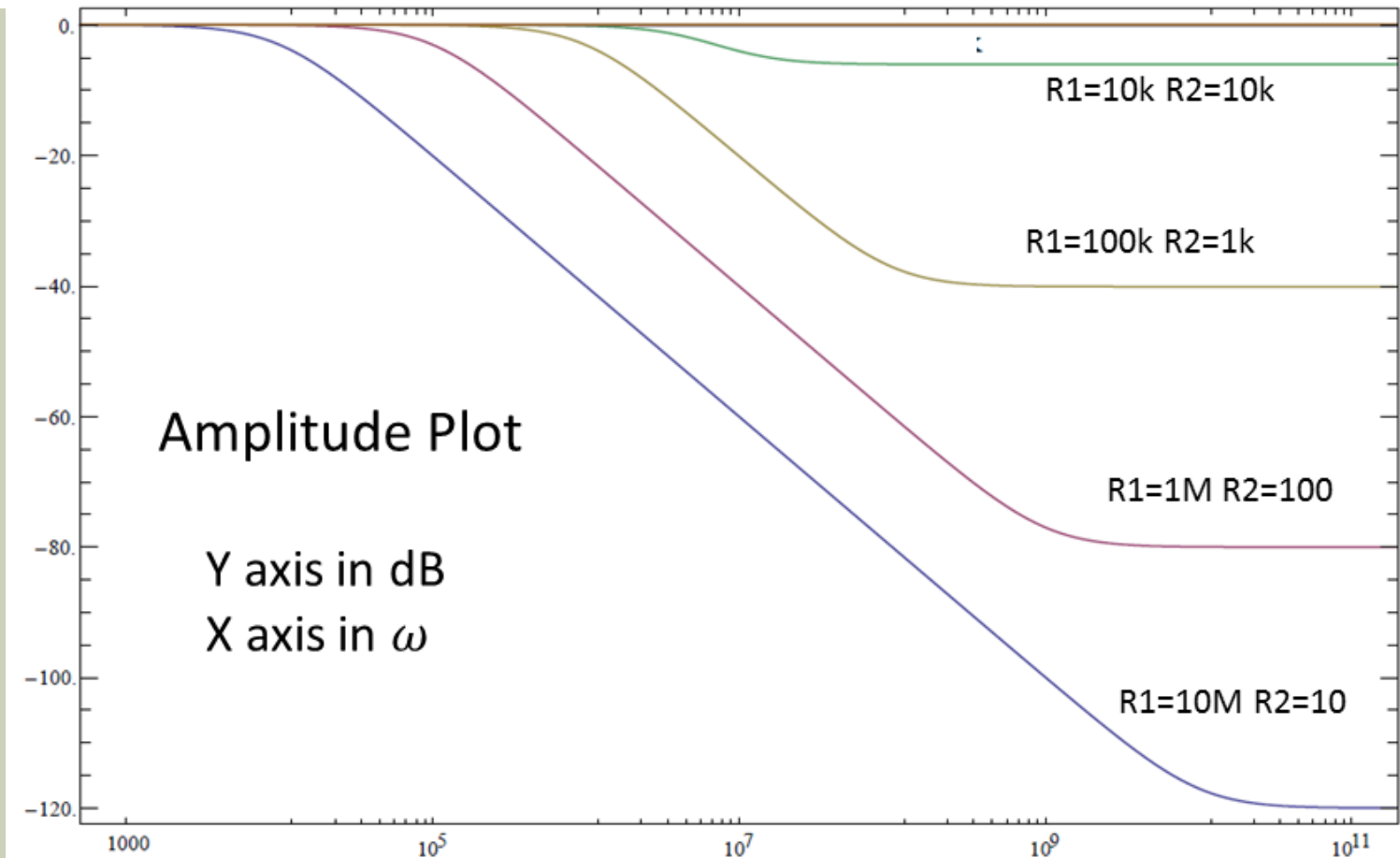
Area under both curves is the same, but the NTF with the resonant peak has less noise within the signal bandwidth.

Low quantization noise within signal bandwidth

Trade-Off

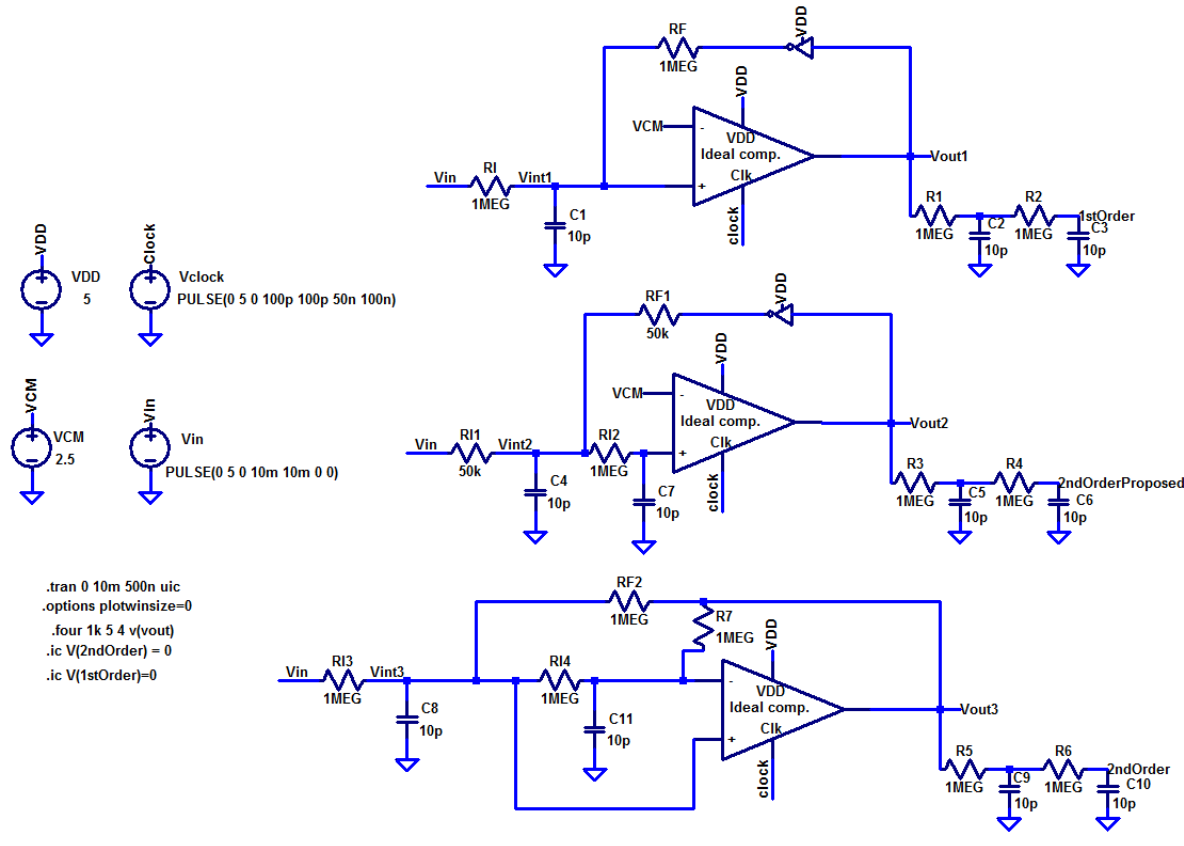
Resonant peak

MATHEMATICA PLOT OF STF



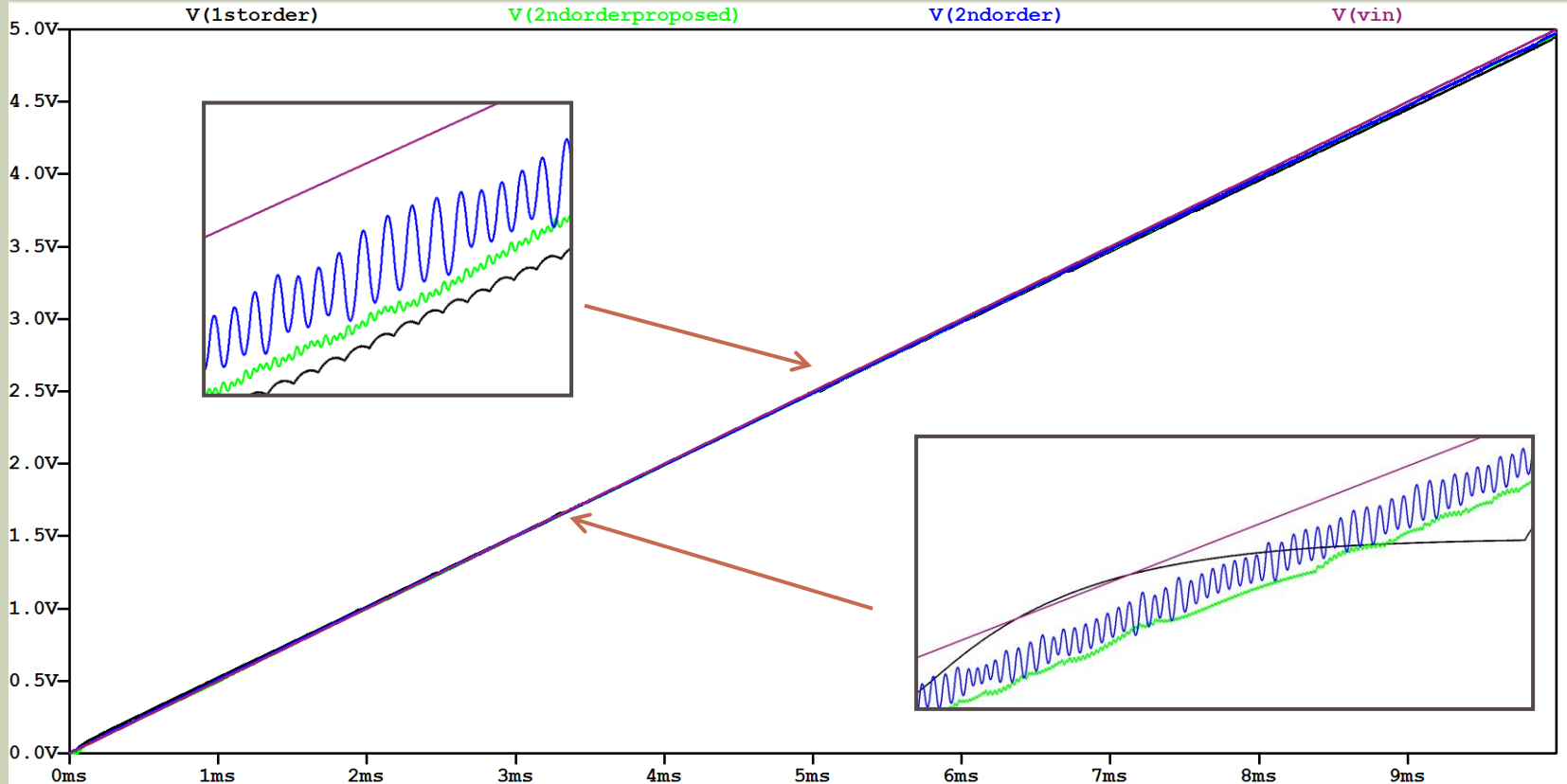
Signal transfer function exhibits 1st order low-pass behavior.

SPICE SIMULATIONS



Each topology was simulated in LTspice using ideal components.

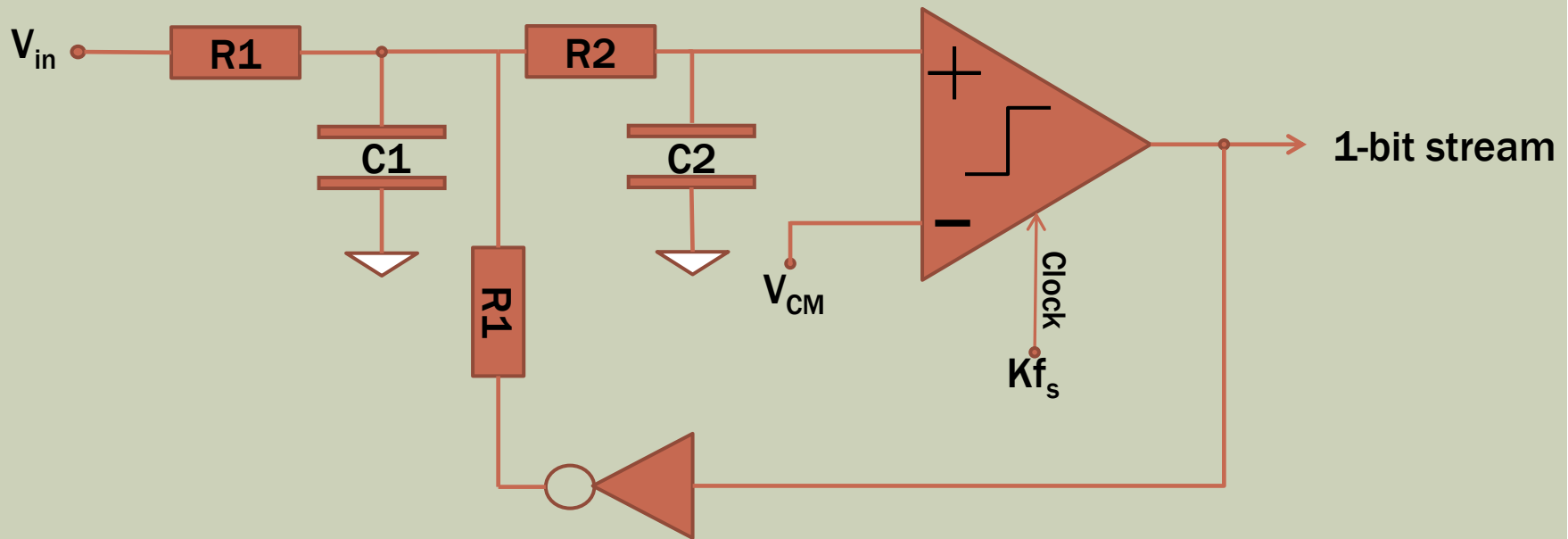
SPICE SIMULATIONS



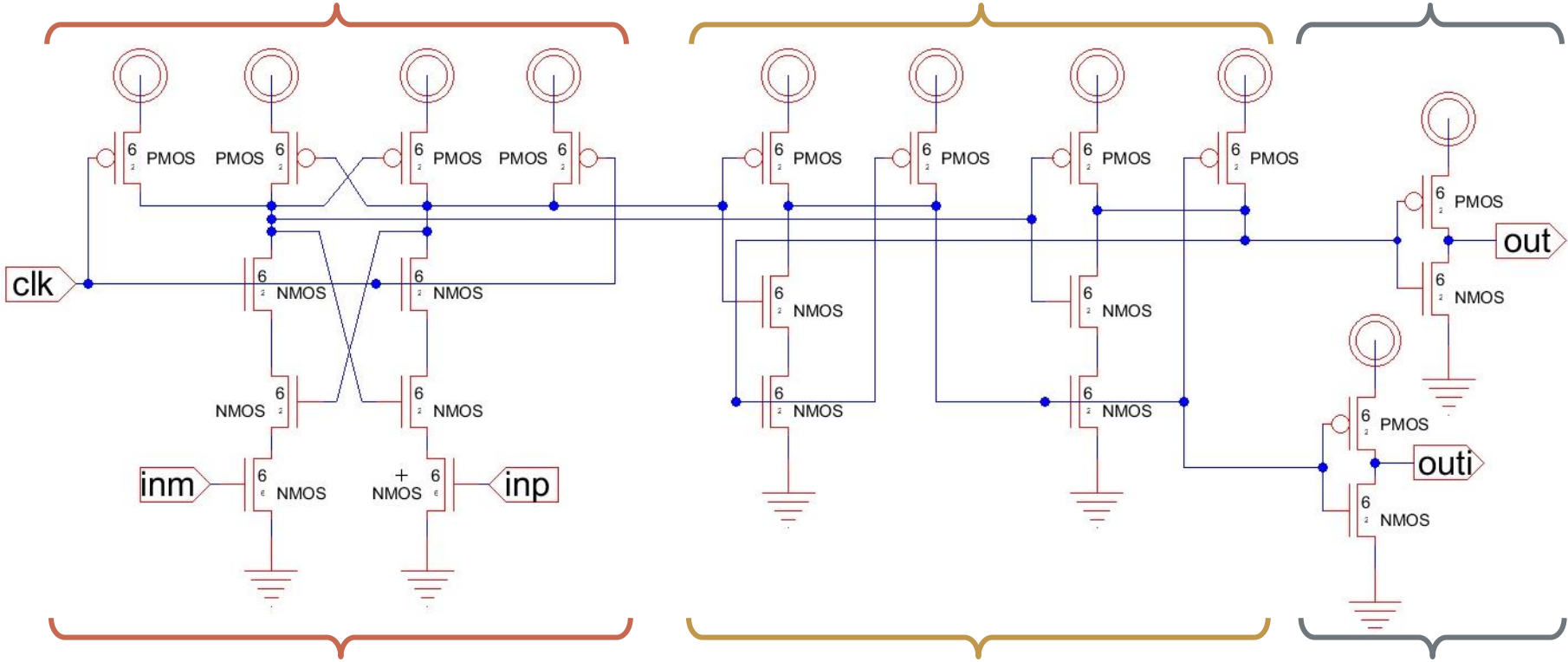
Linearity Comparison of Σ - Δ Modulator Topologies with a 10mS 0-5V Ramp Input

IC IMPLEMENTATION

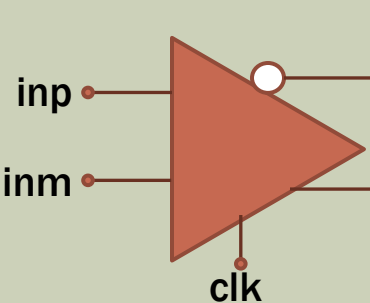
Clocked Comparator



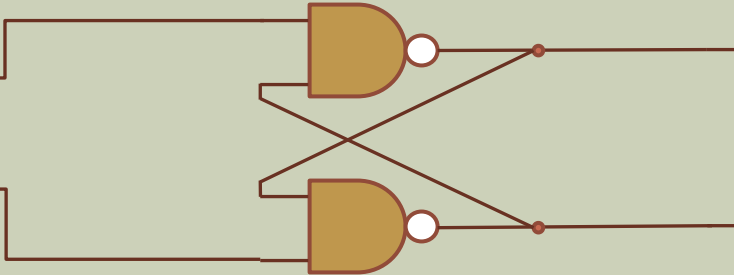
LOW POWER COMPARATOR DESIGN



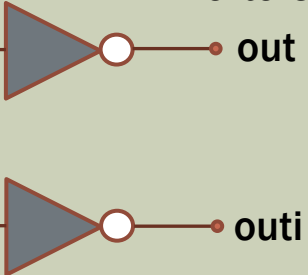
Cross-Coupled Latch



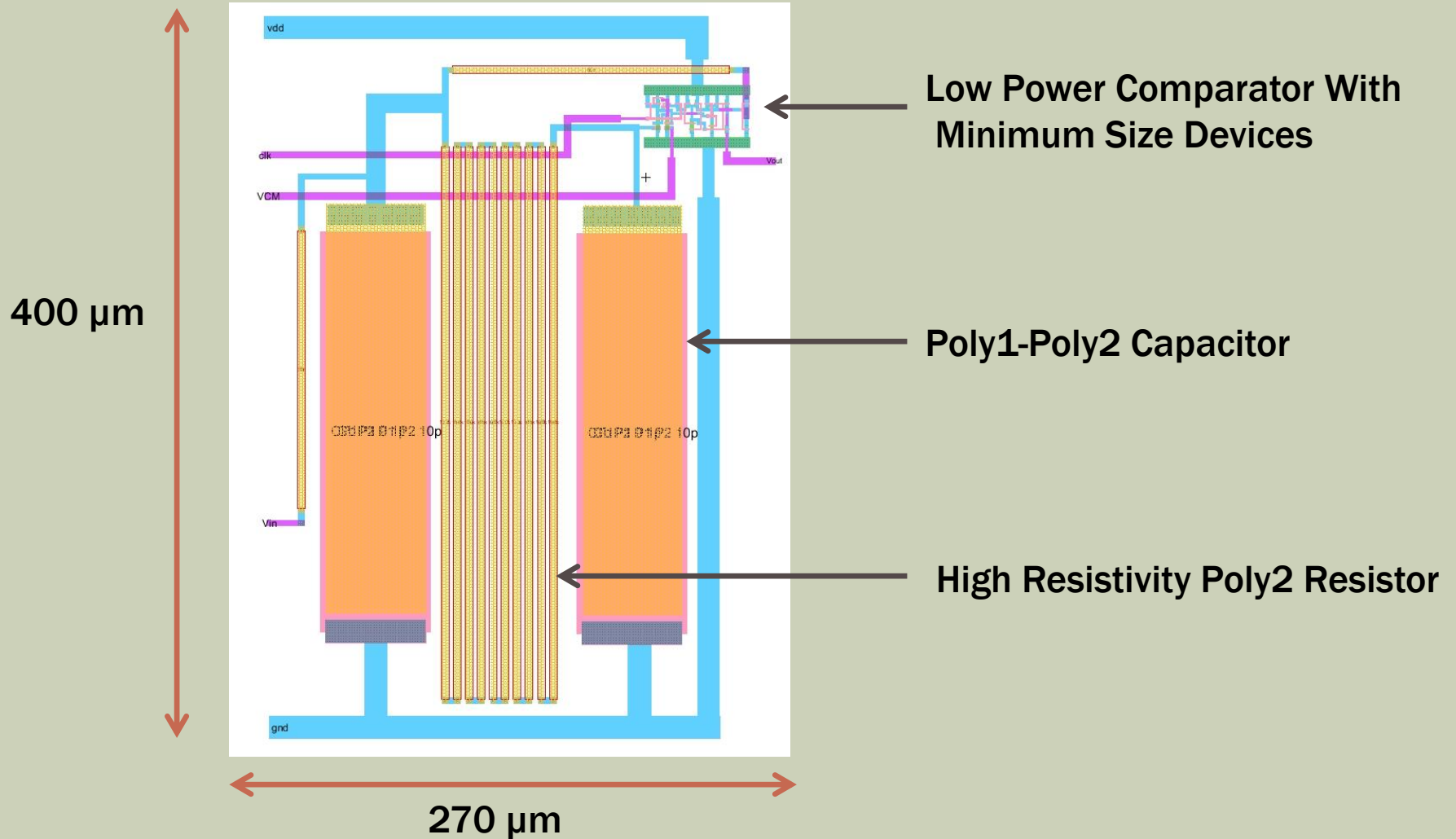
S-R Latch



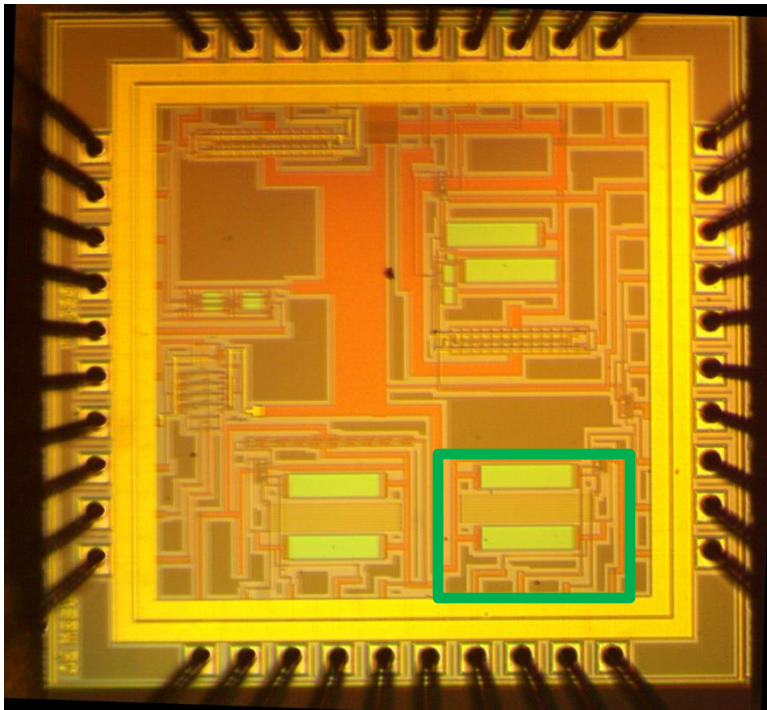
Inverters



CHIP LAYOUT



CHIP MICROGRAPHS



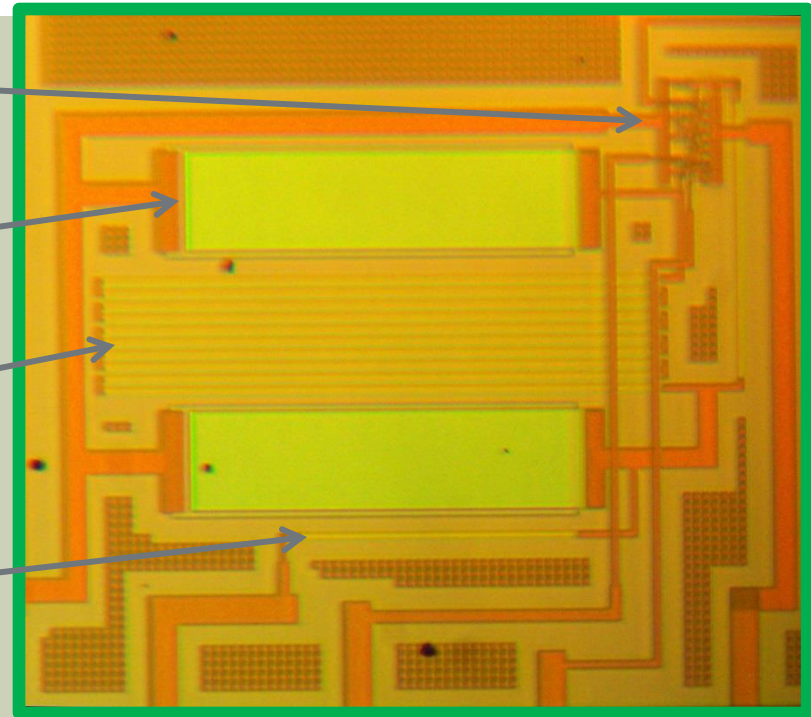
Micrograph of Entire Chip
Area = 1.5 mm^2
Proposed Modulator in Green

Comparator

10pF
Capacitor

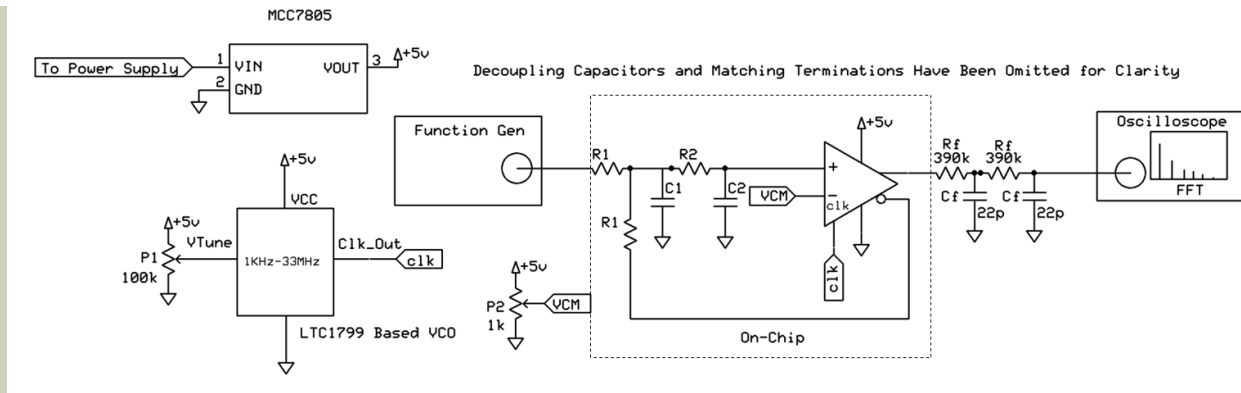
1 M Ω
Resistor

50 k Ω
Resistor

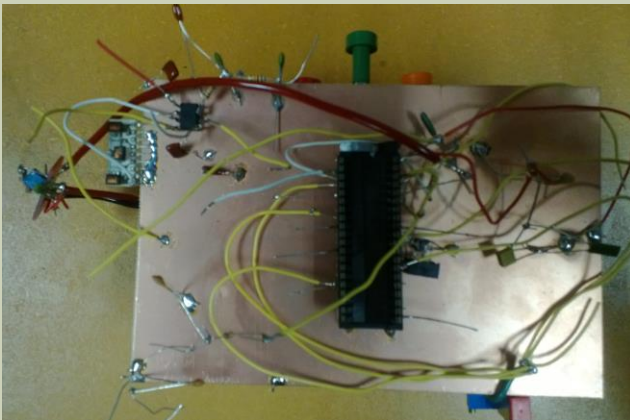


Micrograph of Proposed Modulator
Area in View $\approx 400 \text{ }\mu\text{m}^2$

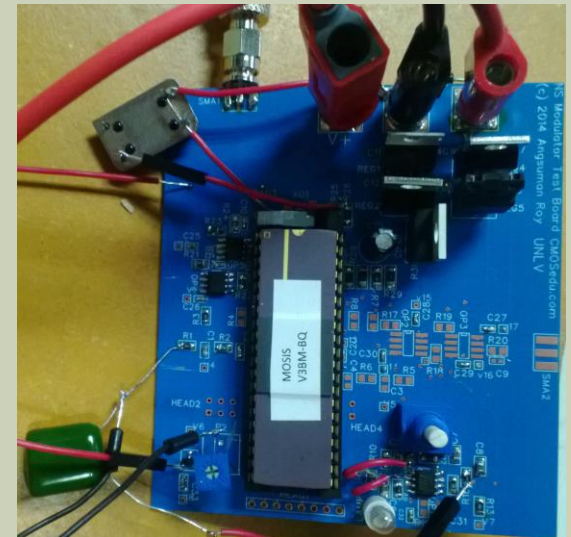
TEST SET-UP



“Dead-bug” Test Set-up

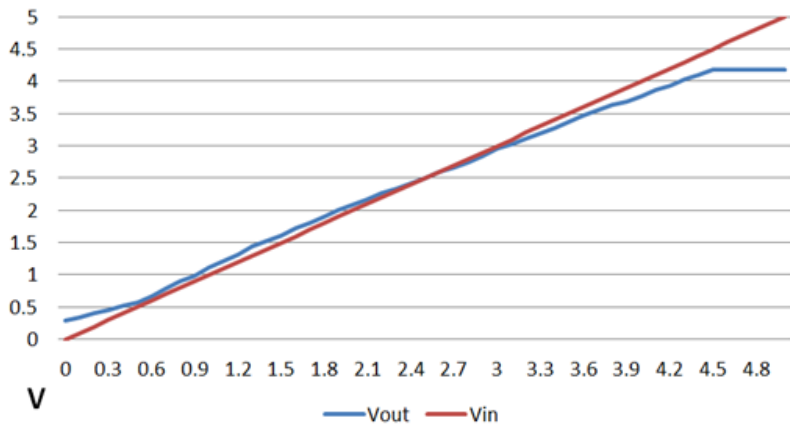


PCB Test Set-up



MEASURED DC TEST RESULTS

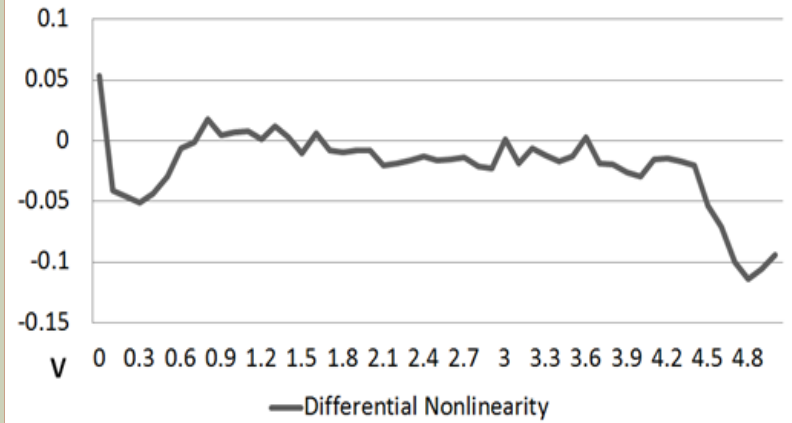
Vin Vs. Vout



DC Transfer

Input and output voltages were compared using a 6.5 digit multimeter.

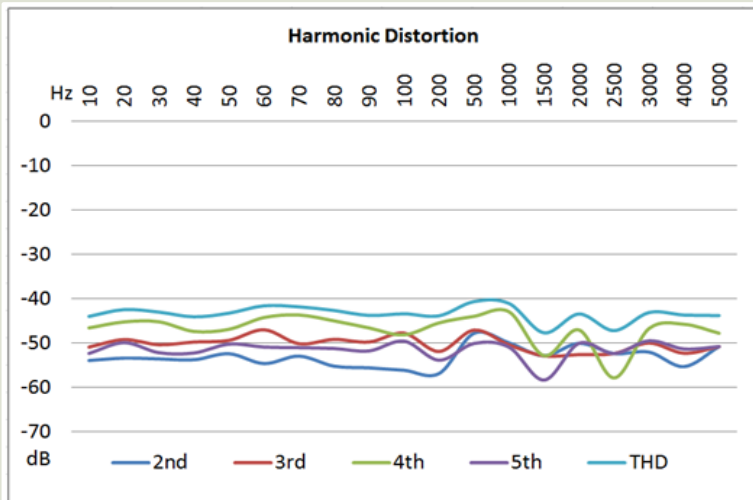
Differential Nonlinearity



% Differential Nonlinearity

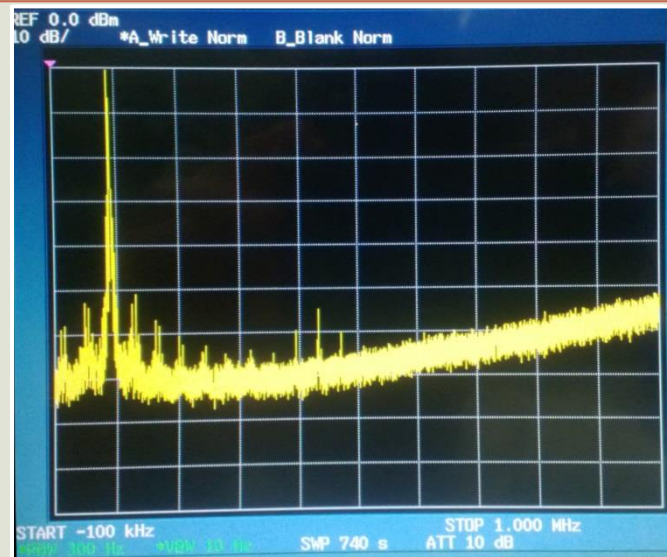
Significant filtering was used to make the output nearly static. DNL was calculated by dividing the measured incremental change by the ideal incremental change between data points.

MEASURED AC TEST RESULTS



Harmonic Distortion (dB Below Fundamental)

Result measured using 8-bit oscilloscope FFT function. This limits SNR to around 50 dB.



Digital Output Viewed on Spectrum Analyzer

Unfiltered digital output with 1kHz sine input. The spurious free dynamic range is 50dB. The noise shaping is clearly visible.

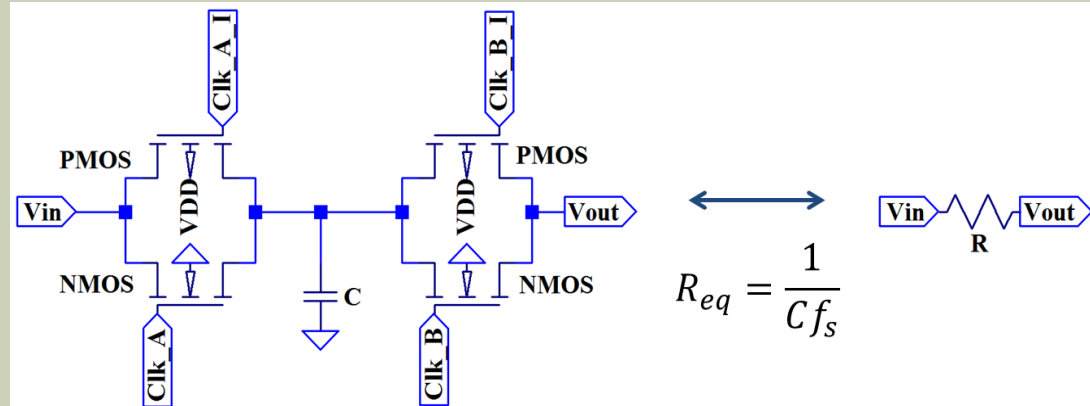
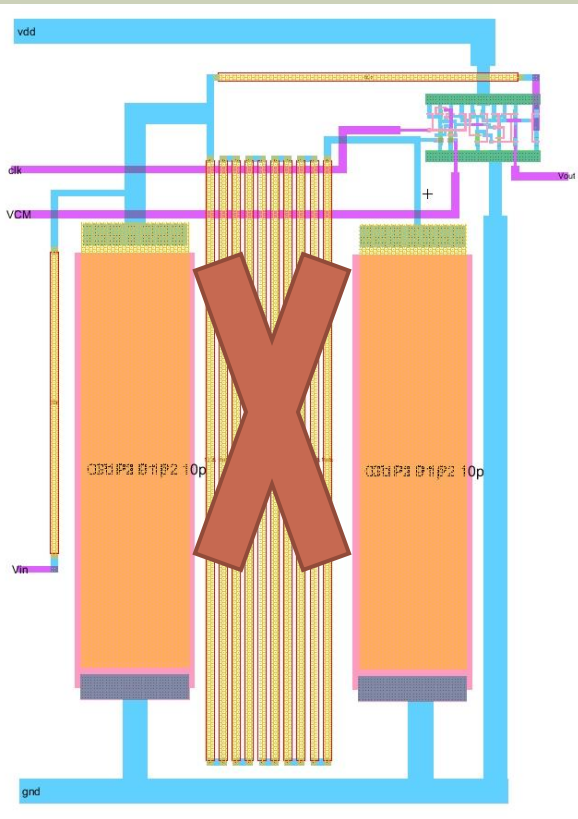
COMPARISONS TO OTHER WORKS

Parameter	2 nd Order Passive Σ - Δ Modulator in This Work (Measured)	2 nd Order Active Σ - Δ Modulator in [5] (Simulated)	2 nd Order Passive Σ - Δ Modulator in [2] (Simulated)
Process	500 nm	350 nm	350 nm
Resolution (ENOB)	8-bit	12-bit	10-bit
Power Consumption	100 μ W (typical) @5V VCC	120 μ W @2V VCC	50 μ W @3.3V VCC
Signal Bandwidth	5 kHz	1 kHz	4 kHz
Clock Frequency	10 MHz	320 kHz	1 MHz

[2] Guessab, S., P. Benabes, and R. Kielbasa. "Passive Delta-Sigma Modulator for Low-Power Applications," *MWSCAS '04*. (2004): 295-298.

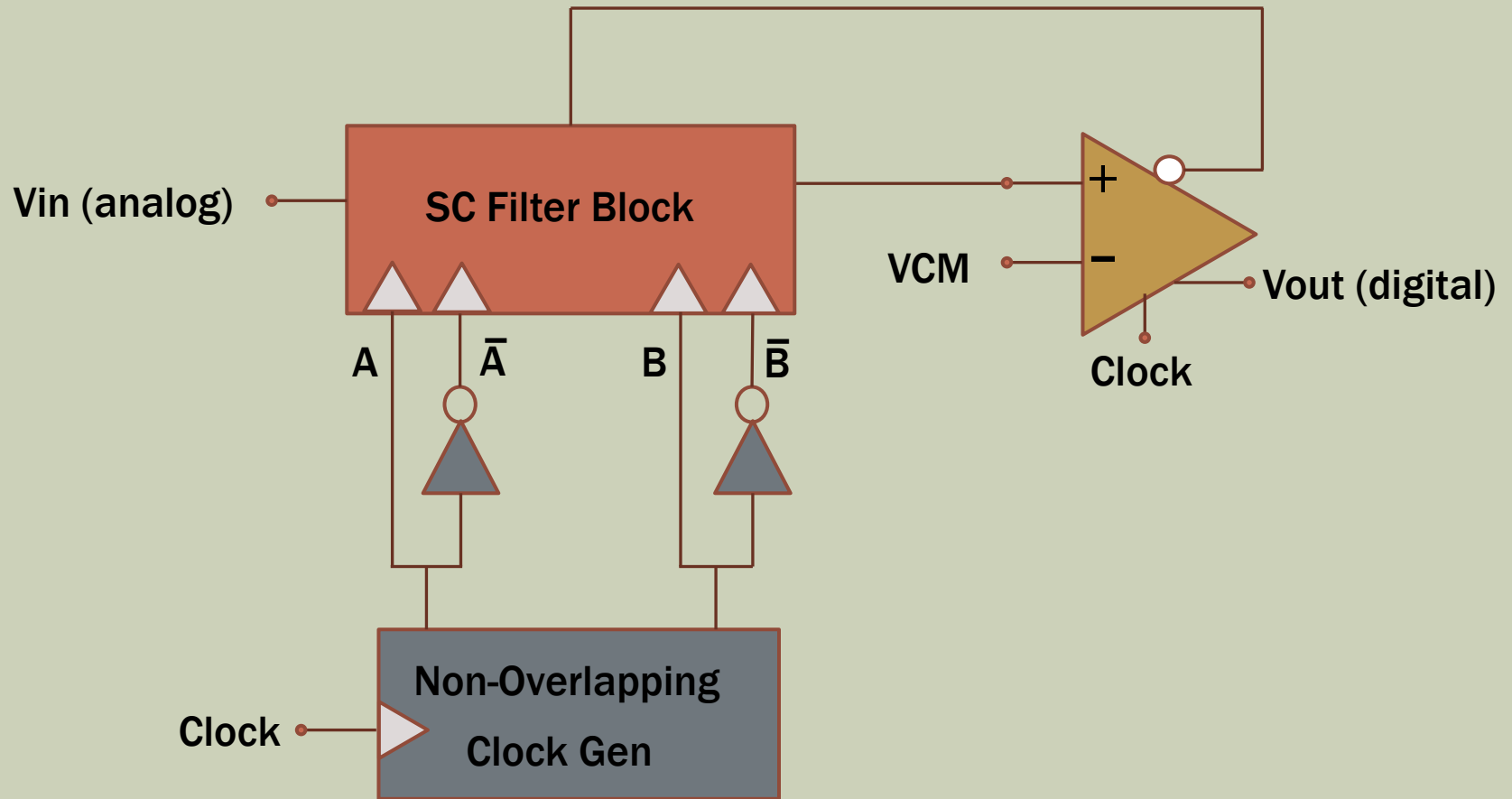
[5] Gundel, Adnan, and Carr, William N. "A Micro Power Sigma-Delta A/D Converter in 0.35 μ m CMOS for Low Frequency Applications," *LISAT 2007*. (2007): 1-7.

SWITCHED CAPACITOR VERSION

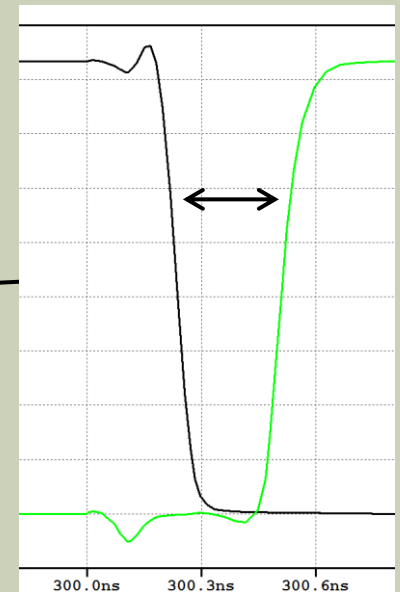
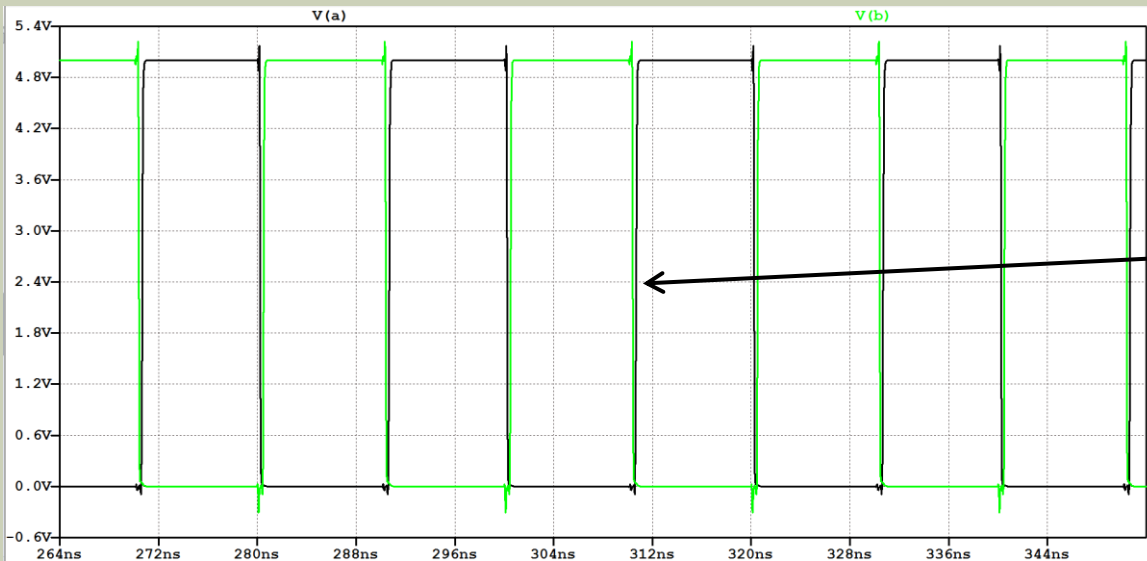
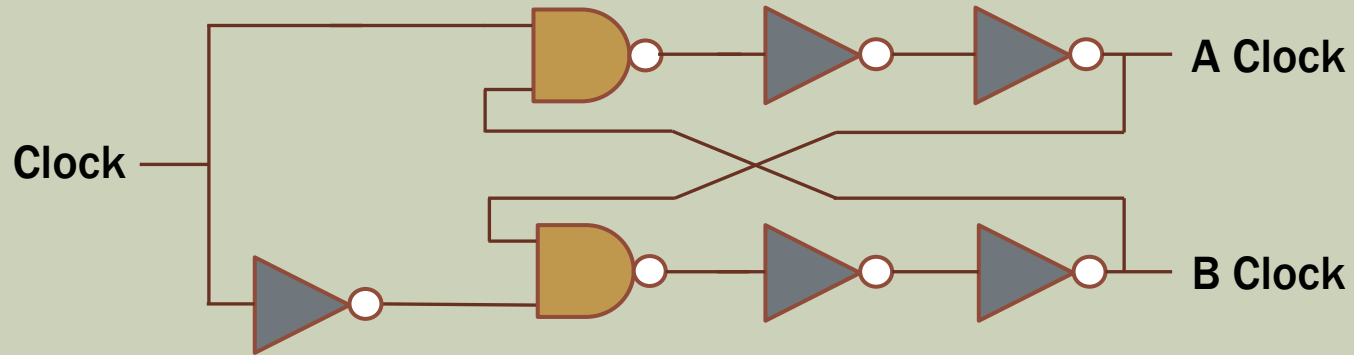


Switched capacitor resistors reduce layout area.

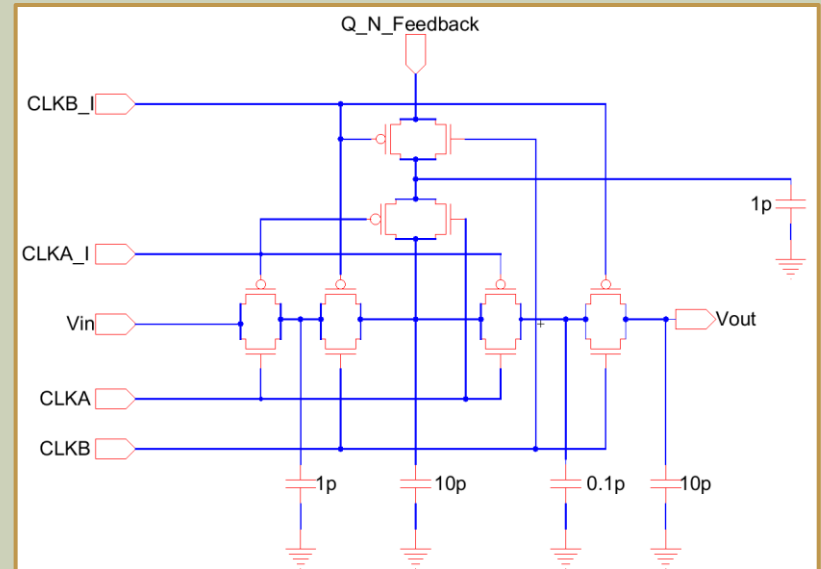
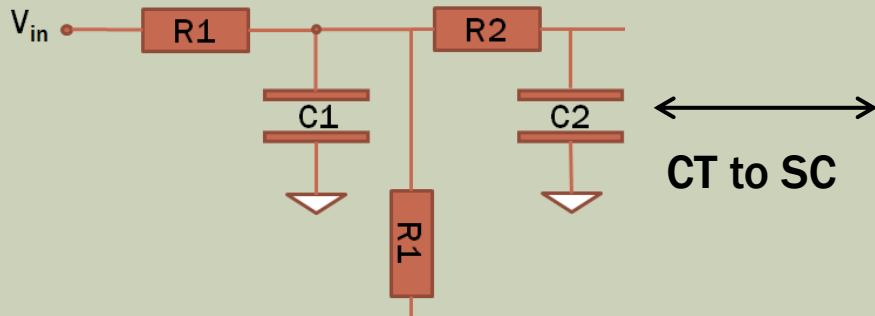
BLOCK DIAGRAM



DESIGN OF NON-OVERLAPPING CLOCK GENERATOR



SWITCHED CAPACITOR FILTER



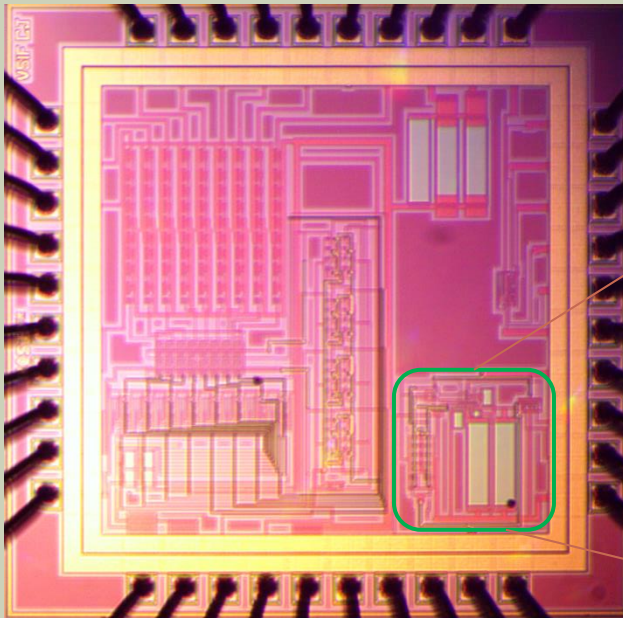
Transmission Gates Used as Switches

- NMOS and PMOS devices are minimum size
- $W/L = 1.8\mu/0.6\mu$

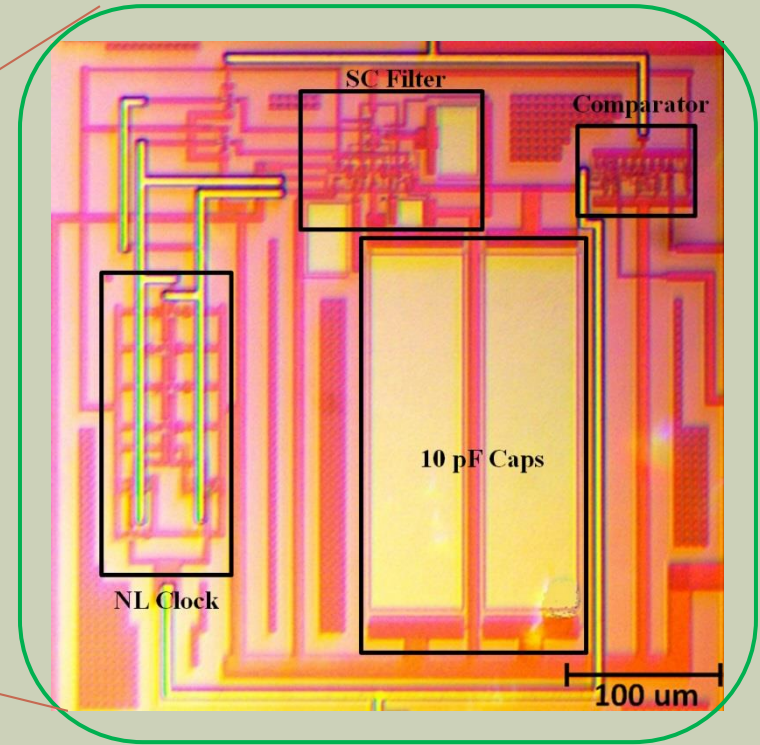
Design is Parasitic Sensitive

- Slight gain error introduced
- Trade off for lower power

FABRICATED CHIP IN 500 NM C5 PROCESS



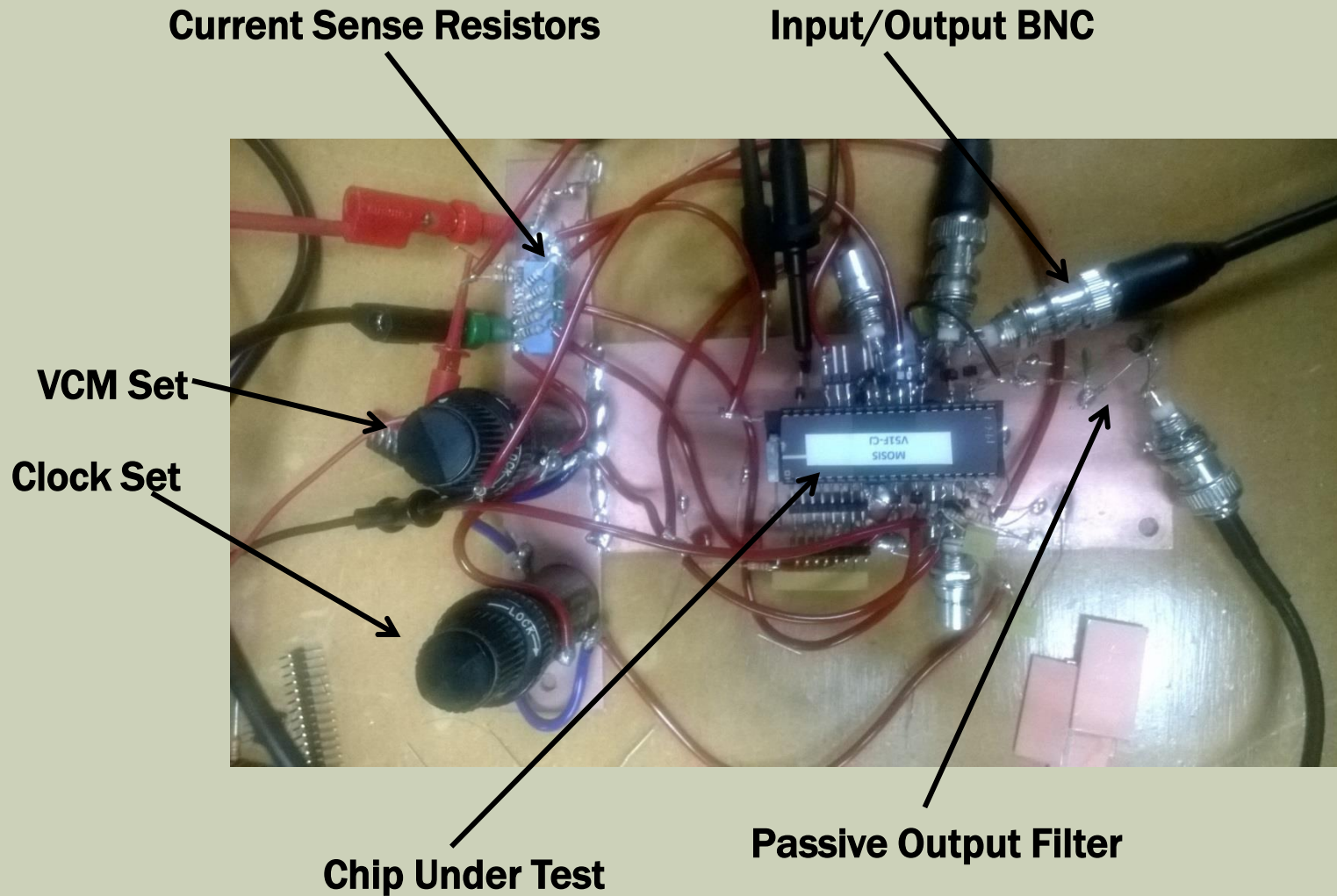
Complete Chip with
Multiple Test Structures



Proposed Σ - Δ Modulator

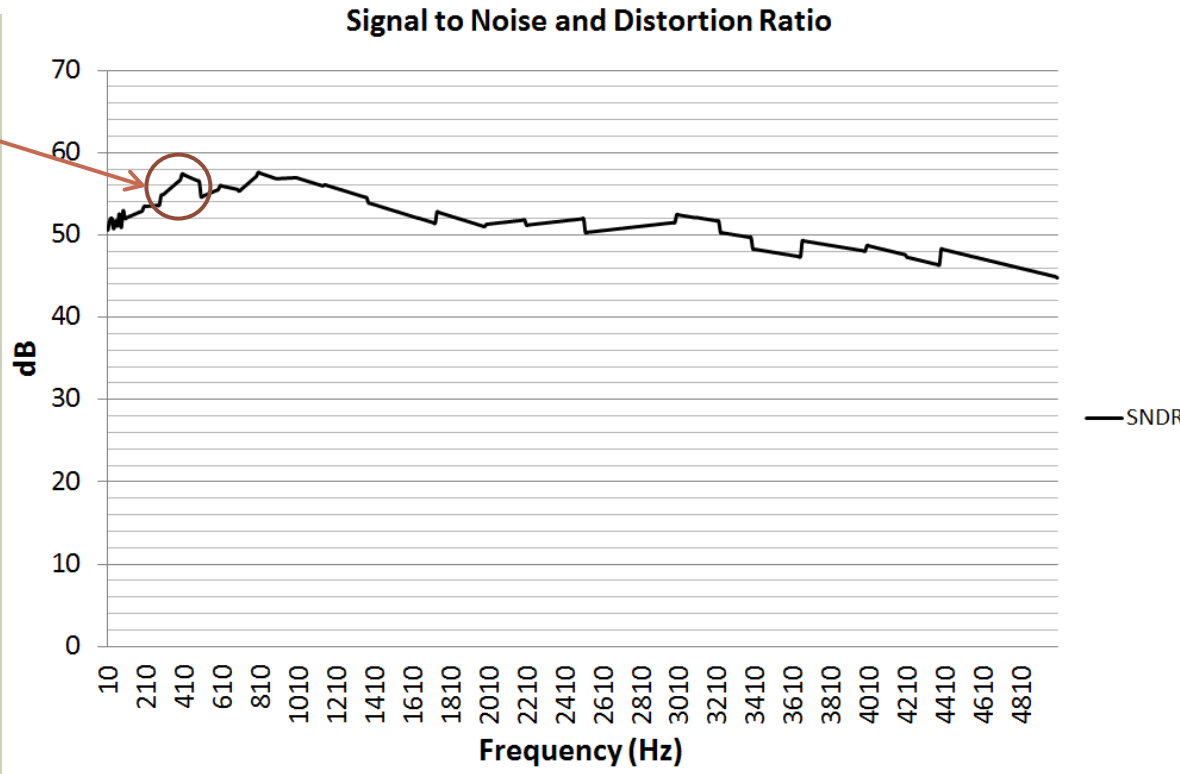
Chips were fabricated with the MOSIS service.

TEST SET-UP



TEST RESULTS

Peak SNDR of 57.6 dB



6.75 μ W
2.5V VDD
2.7 μ A
@ 1 MHz Clock

Test Conditions

Digital output was filtered using a 2nd order passive RC filter.

For each test point filter bandwidth was set to 6X input frequency.

Clock frequency was adjusted to maintain the same OSR.

COMPARISON TO OTHER WORKS

Parameter	Proposed 2 nd -Order SC Σ - Δ Modulator (this work)	2 nd -Order SC Σ - Δ Modulator in [4]	3 rd -Order SC Σ - Δ Modulator in [5]
Process	500 nm	90 nm	130 nm
Resolution (ENOB)	9.3 bits	10.48 bits	12.3 bits
Signal Bandwidth	3 KHz	10 KHz	20 KHz
Clock Frequency	1.024 MHz	1.28 MHz	3.2 MHz
Power Consumption	6.75 μ W @ 2.5 V	17.14 μ W @ 1 V	63 μ W @ 0.4 V
FOM	1.78 pJ/step	0.60 pJ/step	0.31 pJ/step

[4] Hsu, C. H., Tang, K. T., "A 1V Low Power Second-Order Delta-Sigma Modulator for Biomedical Signal Application," *Engineering in Medicine and Biology Society (EMBC), 2013 35th Annual International Conference of the IEEE, pp.2008-2011,, July 2013*

[5] Yoon, Y., Choi, D., Roh, J., " A 0.4-V 63- μ W 76.1-dB SNDR 20-kHz Bandwidth Delta-Sigma Modulator Using a Hybrid Switching Integrator," *IEEE Journal of Solid-State Circuits, vol. no.99, pp.1-12*

K-DELTA-1-SIGMA MODULATOR

New Sigma-Delta Modulator Topology

- First proposed in 2008
- IC implementations used active integrators

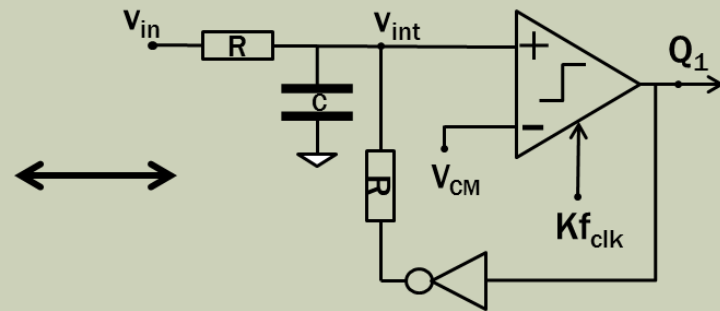
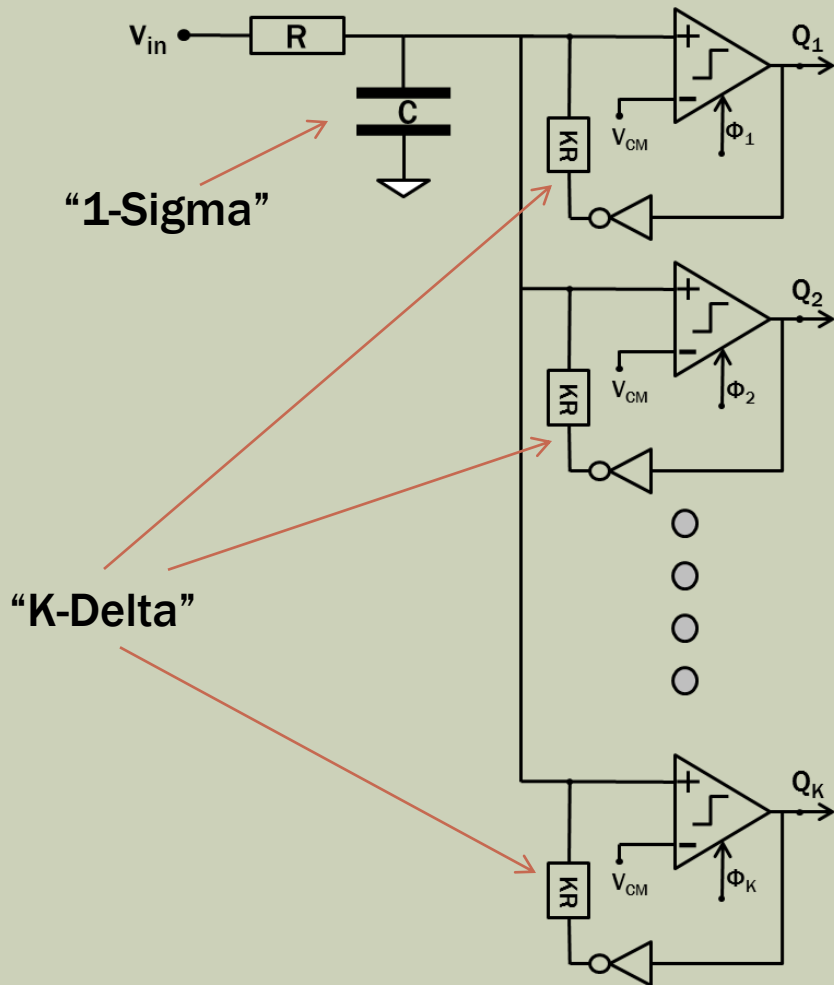
Sampling Rate > Clock Frequency

- Multiple phase shifted clocks are used to increase effective sampling rate.

Passive KD1S

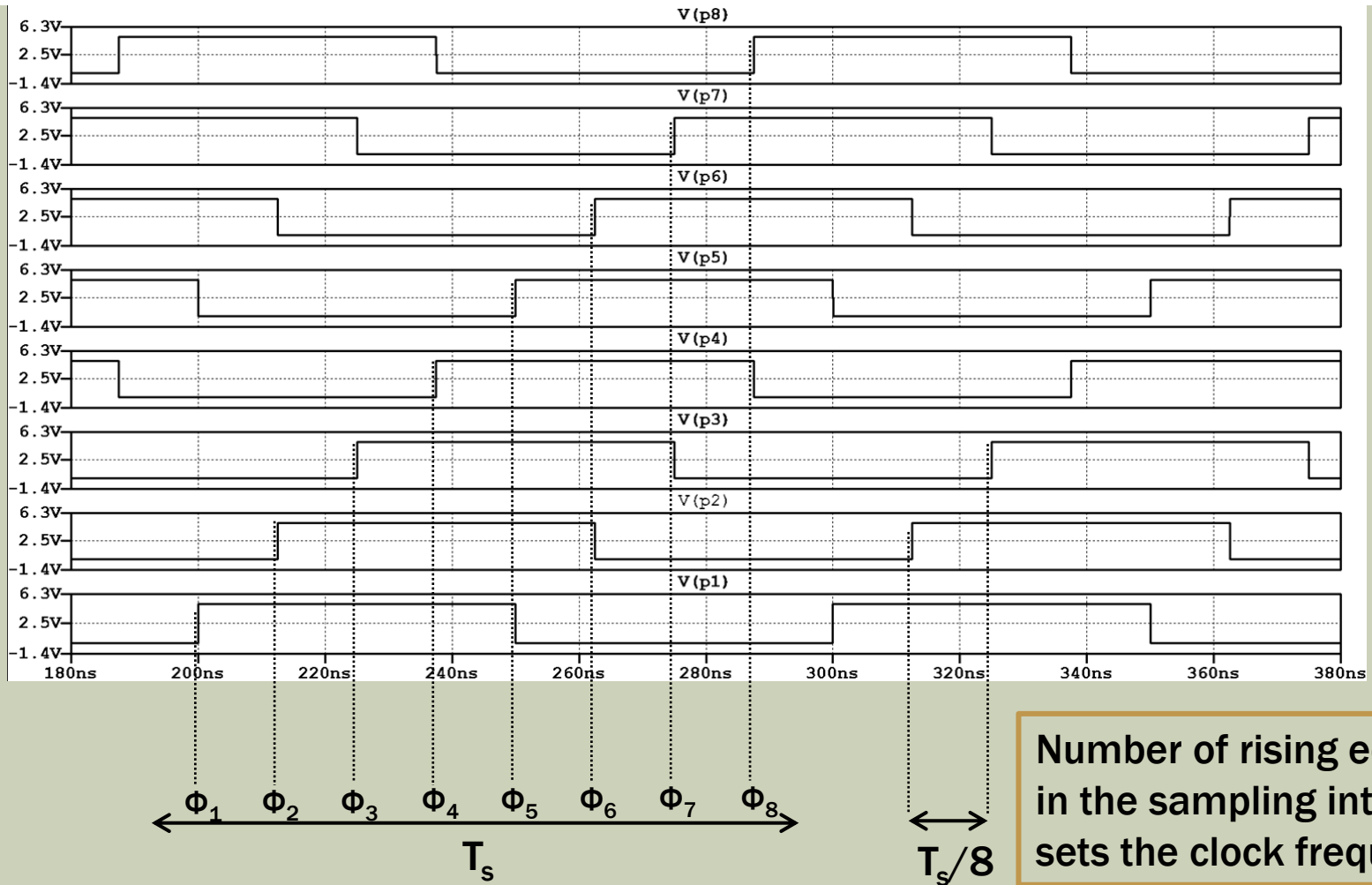
- Passive KD1S modulators are well suited for high-speed applications.

CONCEPTUAL KD1S MODULATOR

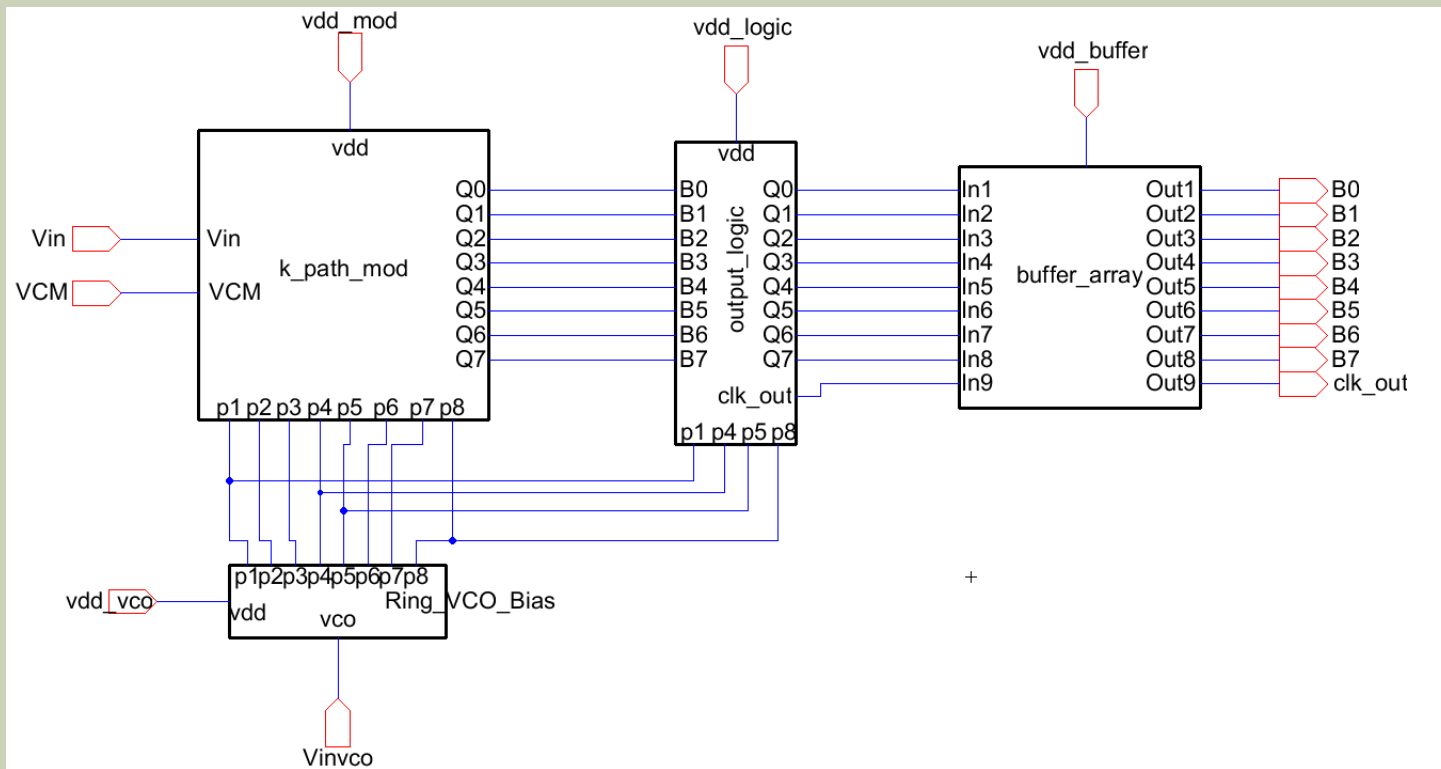


Equivalent to a sigma-delta modulator clocked K times higher.

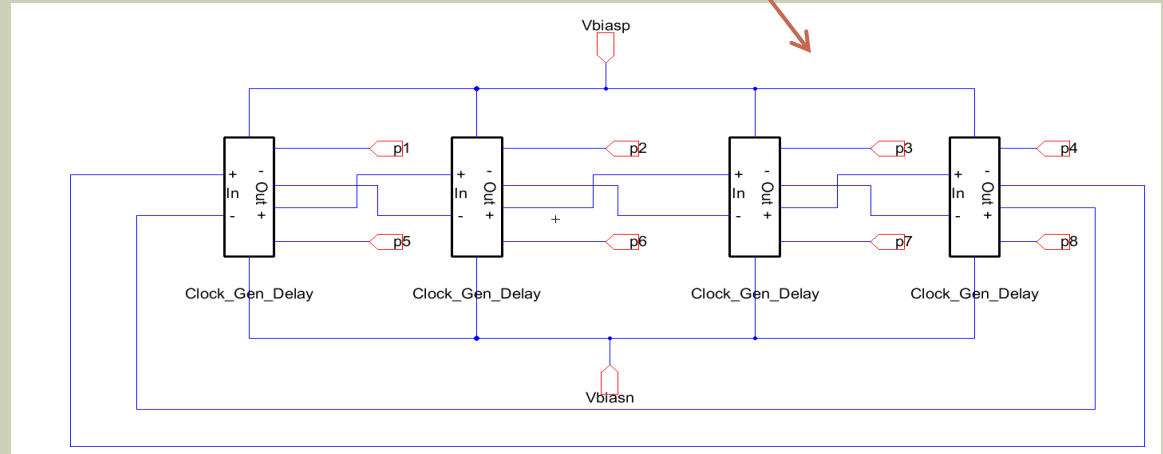
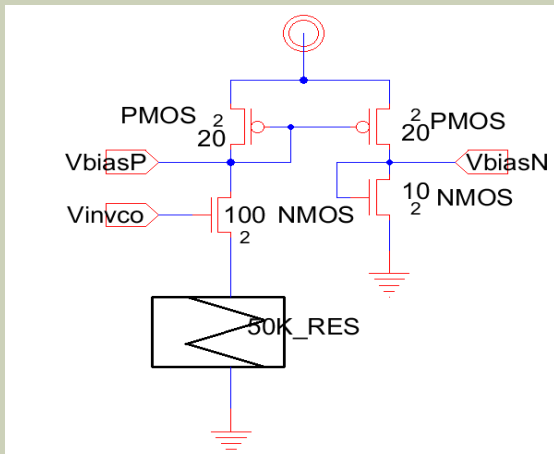
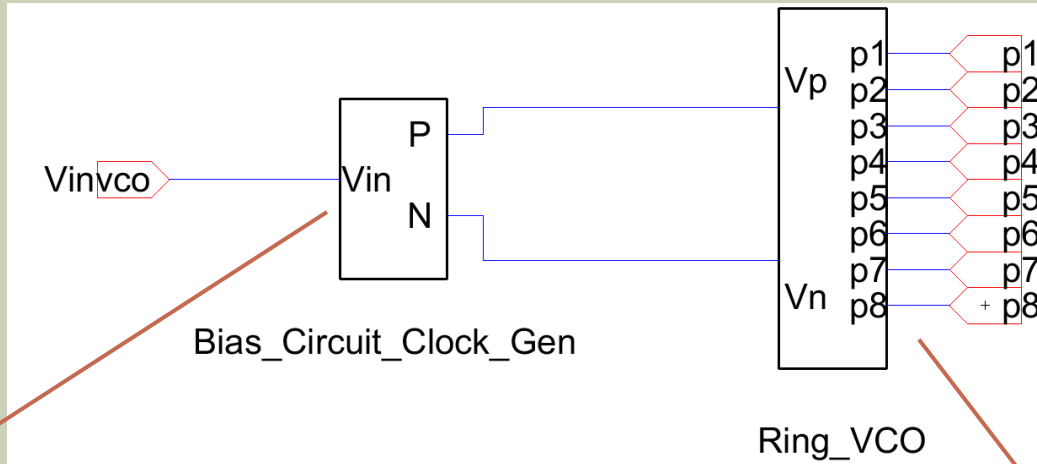
CLOCK PHASES



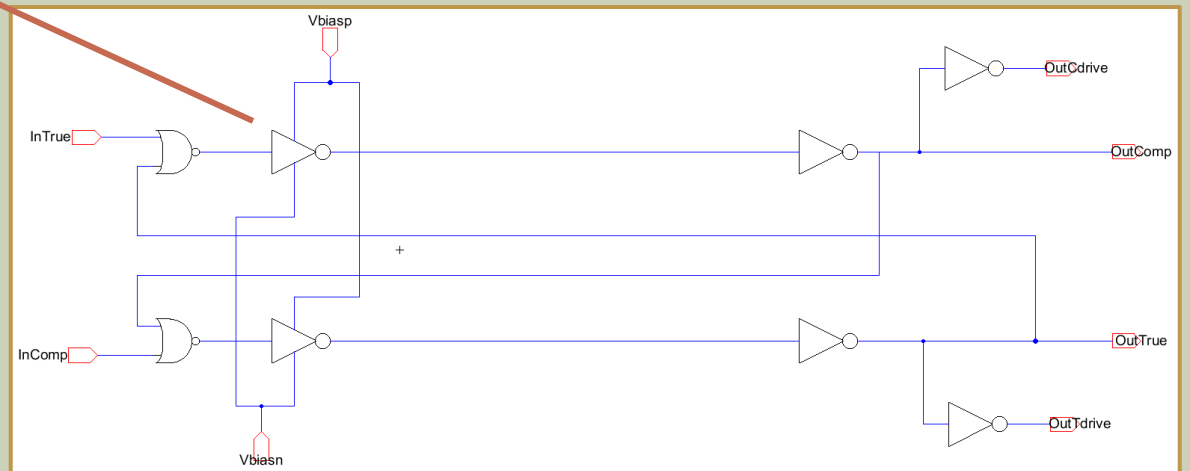
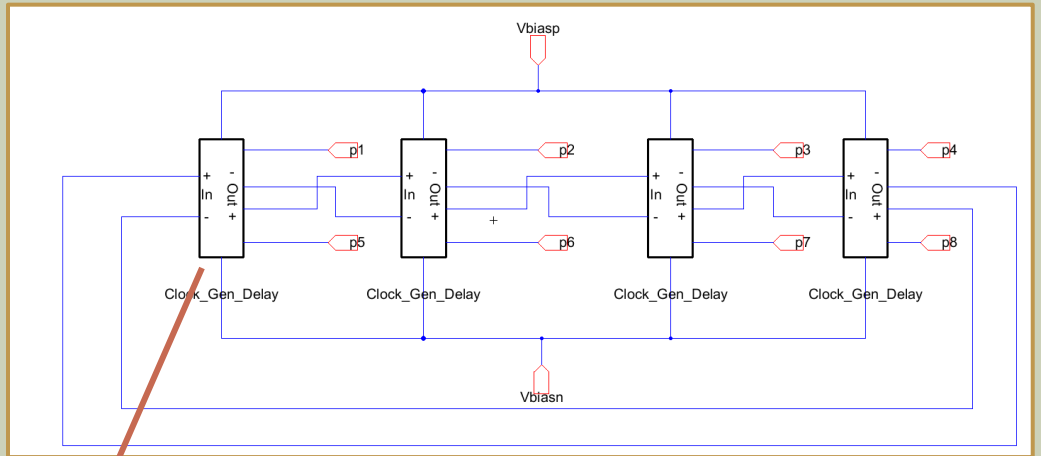
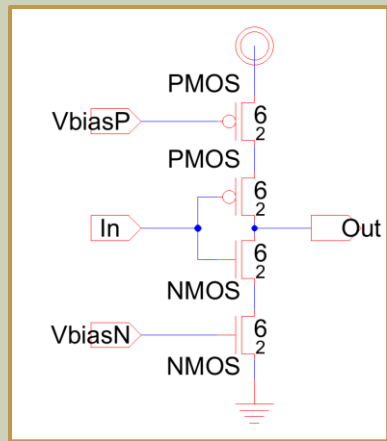
BLOCK DIAGRAM



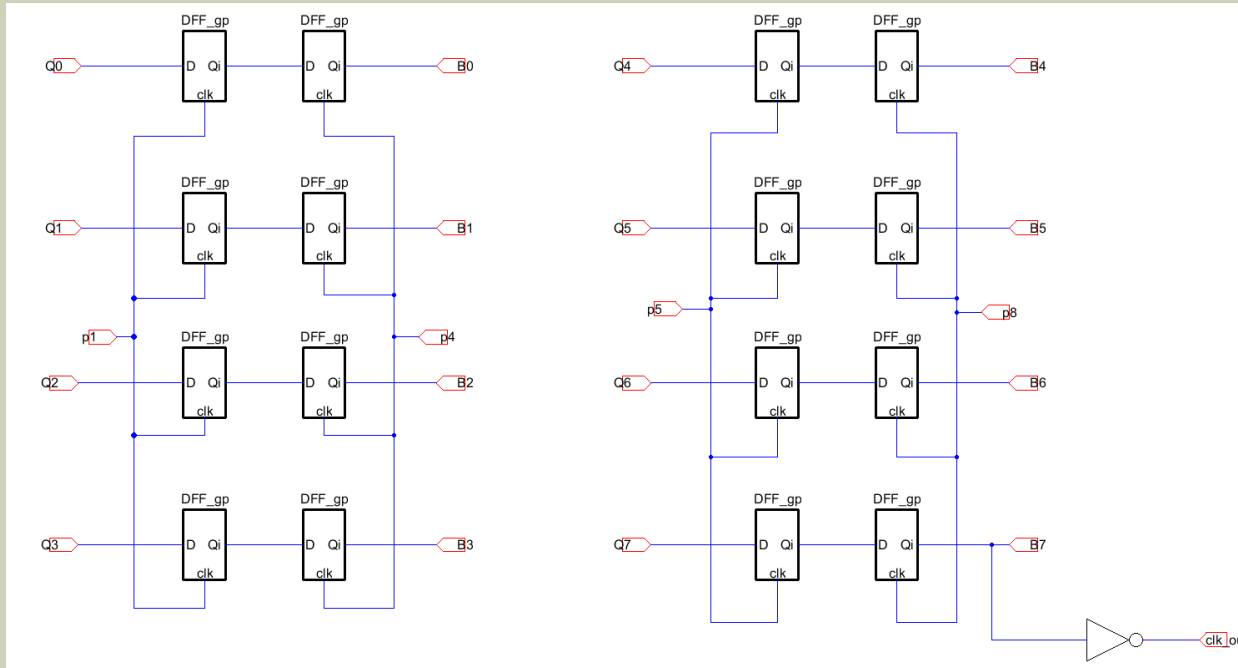
VCO



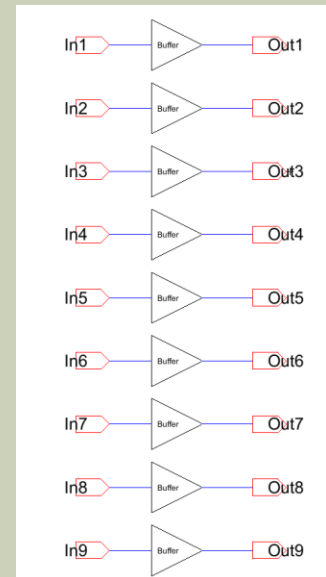
DELAY UNITS



REGISTERS AND BUFFERS



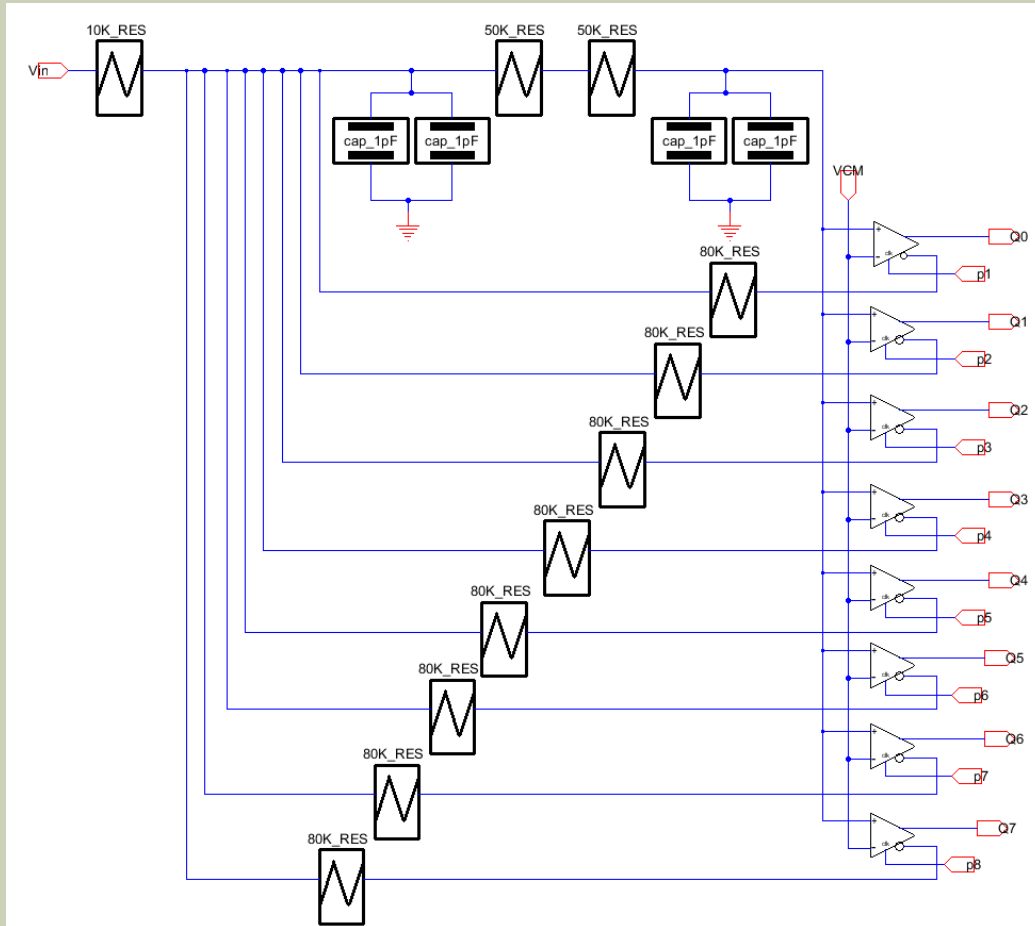
8-bit Register



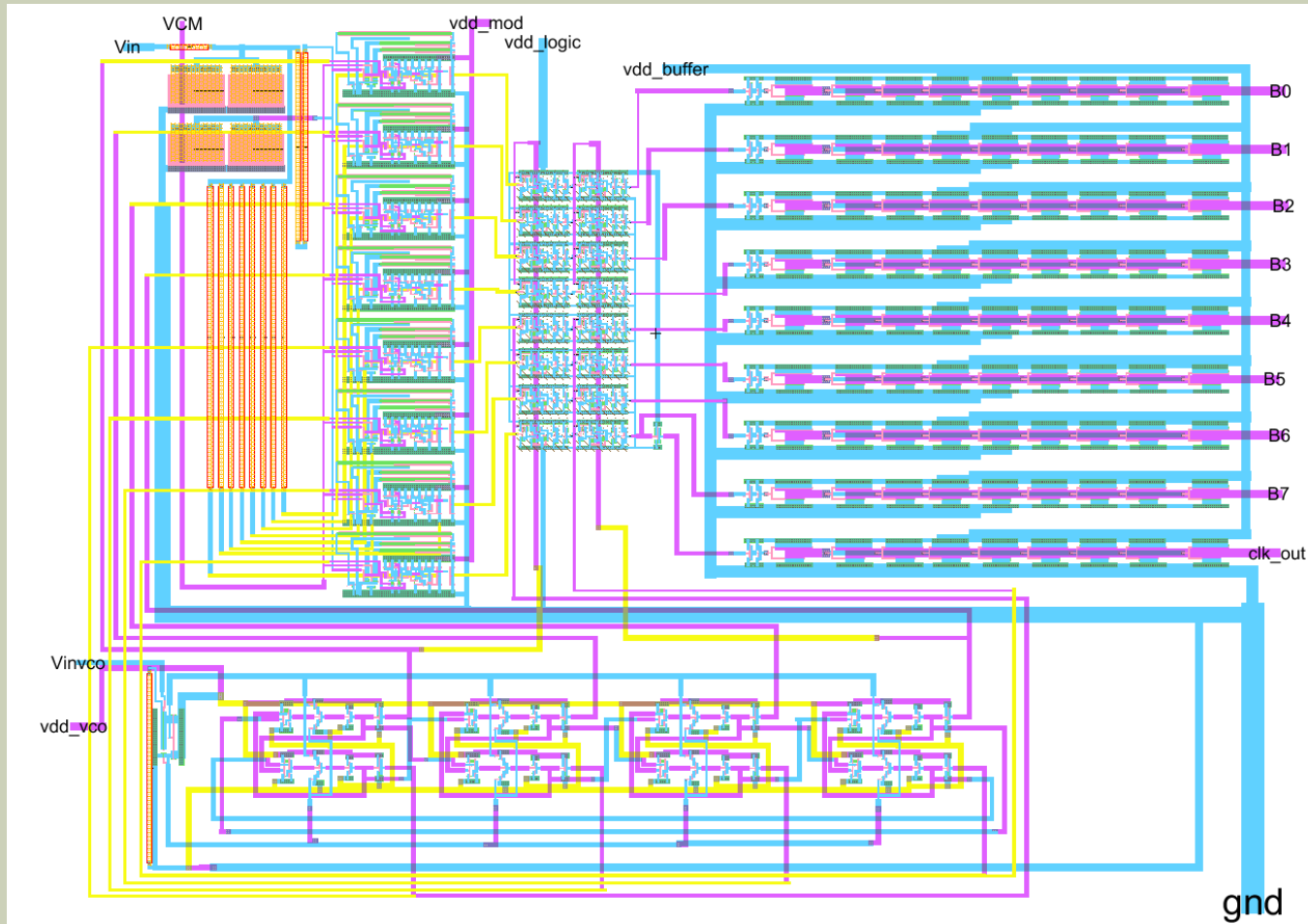
8-bit Buffer

Register is needed to reclock and resynchronize data for further processing.

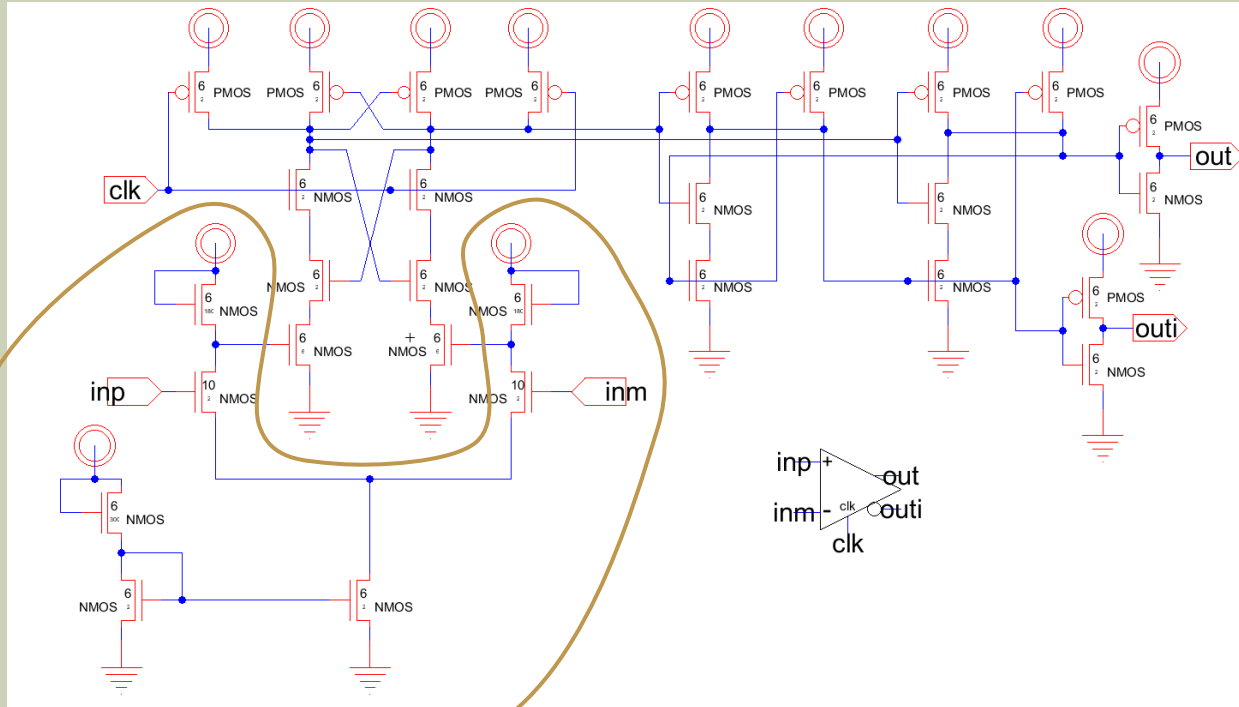
KD1S MODULATOR



LAYOUT IN ELECTRIC VLSI



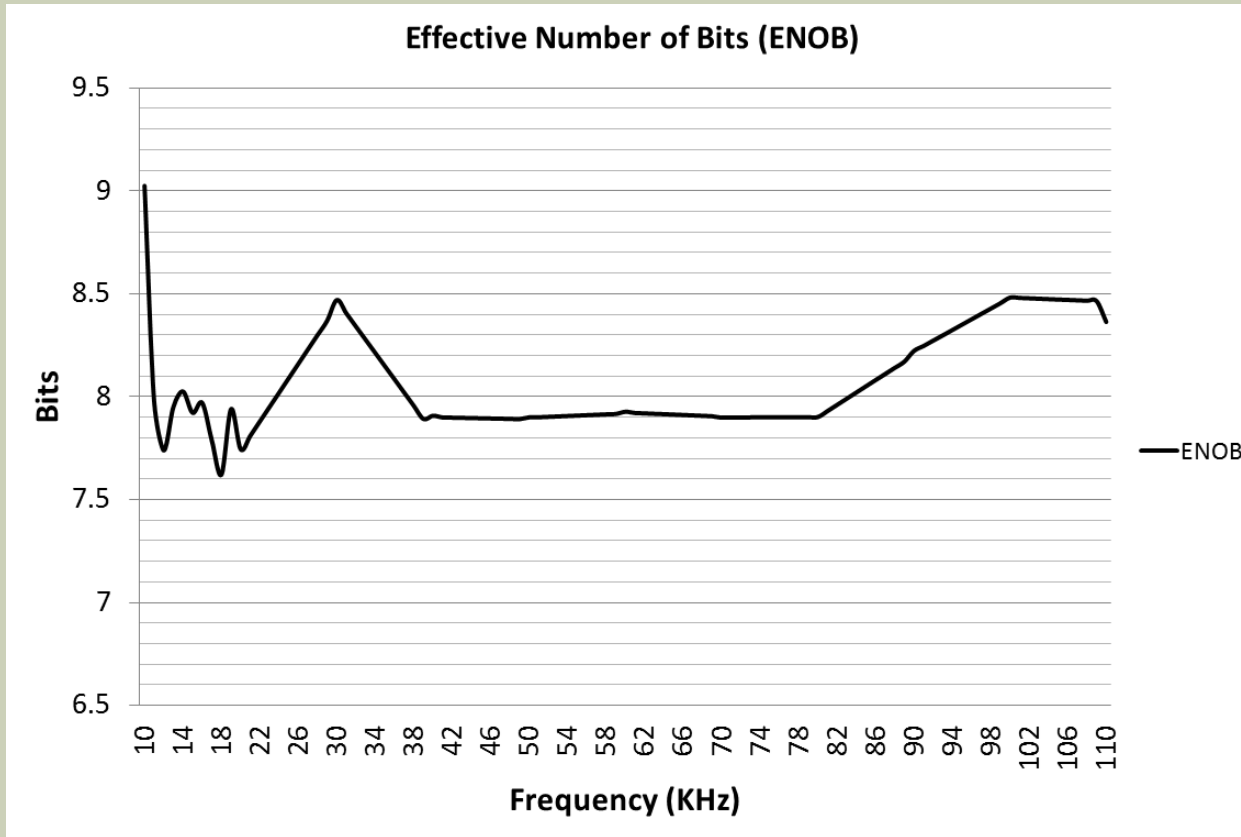
PREAMPED-COMPARATOR



Preamplifier

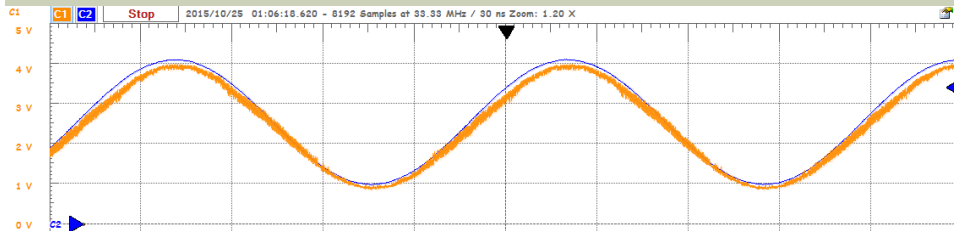
Preamplifier was added to try to increase resolution.

MEASUREMENT RESULTS

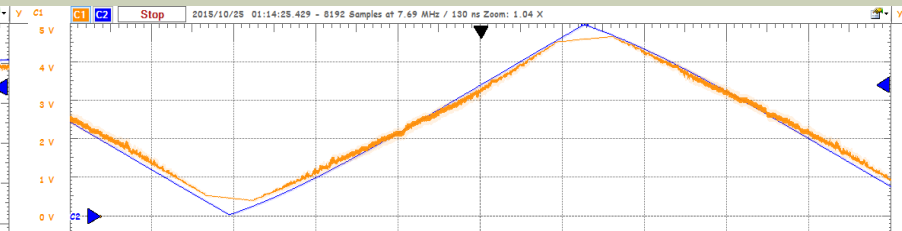


ENOB is derived from SNDR measurements.

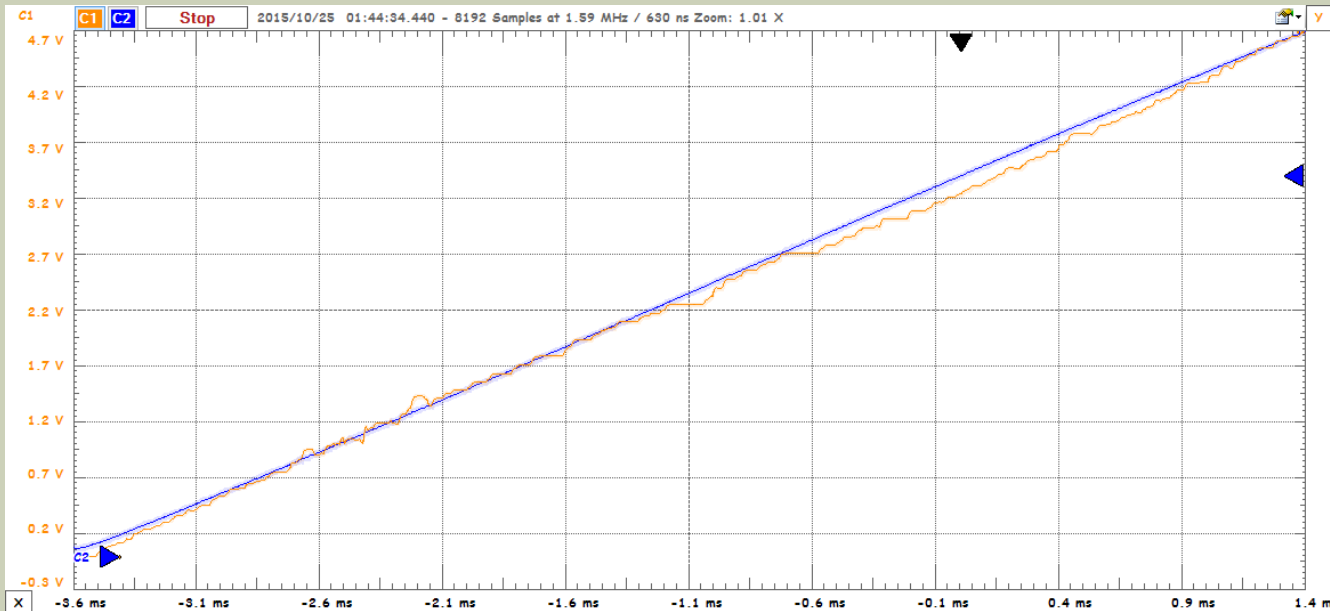
SCOPE TRACES



Sine input and reconstructed output



Ramp for testing input range



Measured transfer function

CONCLUSION

**Good topology for
older CMOS
processes**

**Topology well-suited
for low-power
applications**

**Proposed topology
should scale well to
nm CMOS processes**

**Passive KD1S shows
promise for future
high-speed ADCs**

PUBLICATIONS FROM THIS WORK

Roy, A. and Baker, R. J., "A Passive 2nd-Order Sigma-Delta Modulator for Low-Power Analog-to-Digital Conversion"

IEEE 57th Midwest Symposium on Circuits and Systems 2014

Roy, A., Meza, M., Yurgelon, J. and Baker, R.J. "An FPGA Based Passive K-Delta-1-Sigma Modulator"

IEEE 58th Midwest Symposium on Circuits and Systems 2015

Roy, A. and Baker, R. J., "A Low-Power Switched-Capacitor Passive Sigma-Delta Modulator"

IEEE Dallas Circuits and Systems 2015